

Full Length Research Paper

On the hydrogenation-dehydrogenation of graphene-layer-nanostructures: Relevance to the hydrogen on-board storage problem

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Received 15 September, 2014; Accepted 1 December, 2014

Herein, results of thermodynamic analysis of some theoretical and experimental [thermal desorption (TDS), scanning tunneling microscopy (STM), scanning tunneling spectroscopy (STS), high-resolution electron energy loss spectroscopy/low-energy electron diffraction (HREELS/LEED), photoelectron spectroscopy (PES), angle-resolved photoemission spectroscopy (ARPES), Raman spectroscopy and others] data on “reversible” hydrogenation and dehydrogenation of some graphene-layer-nanostructures are presented. In the framework of the formal kinetics and the approximation of the first order rate reaction, some thermodynamic quantities for the reaction of hydrogen sorption (the reaction rate constant, the reaction activation energy, the per-exponential factor of the reaction rate constant) have been determined. Some models and characteristics of hydrogen chemisorption on graphite (on the basal and edge planes) have been used for interpretation of the obtained quantities, with the aim of revealing the atomic mechanisms of hydrogenation and dehydrogenation of different graphene-layer-systems. The cases of both non-diffusion rate limiting kinetics and diffusion rate limiting kinetics are considered. Some open questions and perspectives remain in solving the actual problem in effective hydrogen on-board storage; using the graphite nanofibers (GNFs) is also considered.

Key words: Epitaxial and membrane graphenes, other graphene-layer-systems, hydrogenation-dehydrogenation, thermodynamic characteristics, atomic mechanisms, the hydrogen on-board efficient storage problem.

INTRODUCTION

As noted in a number of articles 2007 through 2014, hydrogenation of graphene-layers-systems, as a prototype of covalent chemical functionality and an effective tool to open the band gap of graphene, is of both fundamental and applied importance (Geim and Novoselov, 2007; Palermo, 2013).

It is relevant to the current problems of thermodynamic stability and thermodynamic characteristics of the hydrogenated graphene-layers-systems (Sofu et al., 2007; Openov and Podlivaev, 2010; Han et al., 2012), and also to the current problem of hydrogen on-board storage (Akiba, 2011; Zuetzel, 2011; DOE targets, 2012).

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In the case of epitaxial graphene on substrates, such as SiO₂ and others, hydrogenation occurs only on the top basal plane of graphene, and it is not accompanied with a strong (diamond-like) distortion of the graphene network, but only with some ripples. The first experimental indication of such a specific single-side hydrogenation came from Elias et al. (2009). The authors mentioned a possible contradiction with the theoretical results of Sofo et al. (2007), which had down-played the possibility of a single side hydrogenation. They proposed an important facilitating role of the material ripples for hydrogenation of graphene on SiO₂, and believed that such a single-side hydrogenated epitaxial graphene can be a disordered material, similar to graphene oxide, rather than a new graphene-based crystal - the experimental graphane produced by them (on the free-standing graphene membrane).

On the other hand, it is expedient to note that changes in Raman spectra of graphene caused by hydrogenation were rather similar (with respect to locations of D, G, D', 2D and (D+D') peaks) both for the epitaxial graphene on SiO₂ and for the free-standing graphene membrane (Elias et al., 2009).

As it is supposed by many scientists, such a single side hydrogenation of epitaxial graphene occurs, because the diffusion of hydrogen along the graphene-SiO₂ interface is negligible, and perfect graphene is impermeable to any atom and molecule (Jiang et al., 2009). But, firstly, these two aspects are of the kinetic character, and therefore they cannot influence the thermodynamic predictions (Sofo et al., 2007; Boukhvalov et al., 2008; Zhou et al., 2009). Secondly, as shown in the present analytical study, the above noted two aspects have not been studied in an enough degree.

As shown in Elias et al. (2009), when a hydrogenated graphene membrane had no free boundaries (a rigidly fixed membrane) in the expanded regions of it, the lattice was stretched isotropically by nearly 10%, with respect to the pristine graphene. This amount of stretching (10%) is close to the limit of possible elastic deformations in graphene (Nechaev and Veziroglu, 2013), and indeed it has been observed that some of their membranes rupture during hydrogenation. It was believed (Elias et al., 2009) that the stretched regions were likely to remain non-hydrogenated. They also found that instead of exhibiting random stretching, hydrogenated graphene membranes normally split into domain-like regions of the size of the order of 1 μm, and that the annealing of such membranes led to complete recovery of the periodicity in both stretched and compressed domains (Elias et al., 2009).

It can be supposed that the rigidly fixed graphene membranes are related, in some degree, to the epitaxial graphenes. Those may be rigidly fixed by the cohesive interaction with the substrates.

As was noted in Xiang et al. (2010), the double-side hydrogenation of graphene is now well understood, at least from a theoretical point of view. For example, Sofo

et al. (2007) predicted theoretically a new insulating material of CH composition called graphane (double-side hydrogenated graphene), in which each hydrogen atom adsorbs on top of a carbon atom from both sides, so that the hydrogen atoms adsorbed in different carbon sublattices are on different sides of the monolayer plane (Sofo et al., 2007). The formation of graphane was attributed to the efficient strain relaxation for sp^3 hybridization, accompanied by a strong (diamond-like) distortion of the graphene network (Sofo et al., 2007; Xiang et al., 2009). In contrast to graphene (a zero-gap semiconductor), graphane is an insulator with an energy gap of $E_g \approx 5.4$ eV (Openov and Podlivaev, 2010; Lebegue et al., 2009).

Only if hydrogen atoms adsorbed on one side of graphene (in graphane) are retained, we obtain graphone of C₂H composition, which is a magnetic semiconductor with $E_g \approx 0.5$ eV, and a Curie temperature of $T_c \approx 300$ to 400K (Zhou et al., 2009).

As was noted in Openov and Podlivaev (2012), neither graphone nor graphane are suitable for real practical applications, since the former has a low value of E_g , and undergoes a rapid disordering because of hydrogen migration to neighboring vacant sites even at a low temperature, and the latter cannot be prepared on a solid substrate (Podlivaev and Openov, 2011).

It is also expedient to refer to a theoretical single-side hydrogenated graphene (SSHG) of CH composition (that is, an alternative to graphane (Sofo et al. (2007)), in which hydrogen atoms are adsorbed only on one side (Pujari et al., 2011; Dzhurakhalov and Peeters, 2011). In contrast to graphone, they are adsorbed on all carbon atoms rather than on every second carbon atom. The value of E_g in SSHG is sufficiently high (1.6 eV lower than in graphane), and it can be prepared on a solid substrate in principle. But, this quasi-two-dimensional carbon-hydrogen theoretical system is shown to have a relatively low thermal stability, which makes it difficult to use SSGG in practice (Openov and Podlivaev, 2012; Pujari et al., 2011).

As was noted in Pujari et al. (2011), it may be inappropriate to call the covalently bonded SSHG system sp^3 hybridized, since the characteristic bond angle of 109.5° is not present anywhere that is, there is no diamond-like strong distortion of the graphene network, rather than in graphane. Generally in the case of a few hydrogen atoms interacting with graphene or even for graphane, the underlining carbon atoms are displaced from their locations. For instance, there may be the diamond-like local distortion of the graphene network, showing the signature of sp^3 bonded system. However, in SSHGraphene all the carbon atoms remain in one plane, making it difficult to call it sp^3 hybridized. Obviously, this is some specific sp^3 -like hybridization.

The results of Nechaev (2010), and also Table 1A and B in the present paper, of thermodynamic analysis of a number of experimental data point that some specific

Table 1A. Theoretical, experimental and analytical values of some related quantities.

Material	Value/quantity				$K_{0(\text{des.})}, \text{ s}^{-1}$ ($L \approx (D_{\text{app}}/K_{0(\text{des.})})^{1/2}$)
	$\Delta H_{(\text{C-H})} (\text{eV})$	$\Delta H_{(\text{bind.}),} \text{ eV}$	$\Delta H_{(\text{C-C}),} (\text{eV})$	$\Delta H_{(\text{des.})} (\text{eV})$ $\Delta H_{(\text{ads.})} (\text{eV})$	
Graphane CH (Sofa et al. , 2007)	2.5 ± 0.1 (analysis)	6.56 (theory)	2.7 (analysis)		
Graphane CH (Dzhurakhalov and Peeters, 2011)	1.50 (theory)	5.03 (theory)	2.35 (analysis)		
Graphane CH (Openov and Podlivaev, 2010)	2.46 ± 0.17 (analysis)			2.46 ± 0.17 (theory)	2.0 × 10 ¹⁵ (analysis)
Free-standing graphene-like membrane (Elias et al., 2009)	There are no experimental values in the work			if 2.5 ± 0.1	then 7 × 10 ¹²
				if 2.6 ± 0.1 (1.0 ± 0.2) (analysis)	then 5 × 10 ¹³ ($K_{0(\text{ads.})} \approx K_{0(\text{des.})}$)
Hydrogenated epitaxial graphene (Elias et al., 2009)	There are no experimental values in the work			then 1.84	if 7 × 10 ¹²
				then 1.94	if 5 × 10 ¹³
Hydrogenated epitaxial* graphene, TDS-peak #1 (Elias et al., 2009)				if 0.3	then 0.2
				if 0.6	then 80
Hydrogenated epitaxial* graphene, TDS-peak #2 (Elias et al., 2009)				if 0.9	then 3.5 × 10 ⁴
				(0.3 ± 0.2) (analysis)	($K_{0(\text{ads.})} \approx K_{0(\text{des.})}$) ($L \sim d_{\text{sample}}$)
Hydrogenated epitaxial* graphene, TDS-peak #3 (Elias et al., 2009)				0.6 ± 0.3 (as processes ~ I-II, ~ model "G", Figure 4) (analysis)	2 × 10 ⁷ (or 2 × 10 ³ - 2 × 10 ¹¹) ($L \sim d_{\text{sample}}$) (analysis)
				0.6 ± 0.3 (as for processes ~I-II, ~model "G", Figure 4) (analysis)	1 × 10 ⁶ (or 4 × 10 ² - 2 × 10 ⁹) ($L \sim d_{\text{sample}}$) (analysis)
Rigidly fixed hydrogenated graphene membrane (Elias et al., 2009)	There are no experimental values in the work			There are no experimental values in the work	There are no experimental values in the work
Graphene (Dzhurakhalov and Peeters, 2011)		7.40 (theory)	4.93 (analysis)		
Graphite (Nechaev and Veziroglu, 2013)		7.41 ± 0.05 (analysis)	4.94 ± 0.03 (analysis)		
Diamond (Nechaev and Veziroglu, 2013)		7.38 ± 0.04 (analysis)	3.69 ± 0.02 (analysis)		

Table 1B. Theoretical, experimental and analytical values of some related quantities.

Material	Value/quantity			
	$\Delta H_{(C-H)}$, eV	$\Delta H_{(C-C)}$, eV	$\Delta H_{(des.)}$, eV	$K_0_{(des.)}$, s ⁻¹
Hydrofullerene C ₆₀ H ₃₆ (Pimenova et al., 2002)	2.64 ± 0.01 (experiment)			
Hydrogenated carbon nanotubes C ₂ H (Bauschlicher and So, 2002)	2.5 ± 0.2 (theory)			
Hydrogenated isotropic graphite, graphite nanofibers and nanostructured graphite (Nechaev, 2010)	2.50 ± 0.03 (analysis, process III, model "F*")	4.94 ± 0.03 (analysis)	2.6 ± 0.03 (analysis, process III)	There are empirical values in the work (analysis of experiment)
Hydrogenated isotropic graphite, graphite nano-fibers, nanostructured graphite, defected carbon nanotubes (Nechaev, 2010)	2.90 ± 0.05 [analysis, process II, models "H", "G" (Figure 4)]		1.24 ± 0.03 (analysis, process II)	There are empirical values in the work (analysis of experiment)
Hydrogenated isotropic graphite, carbon nanotubes (Nechaev, 2010)	2.40 ± 0.05 [analysis, process I, models "F", "G" (Figure 4)]		0.21 ± 0.02 (analysis, process I)	There are empirical values in the work (analysis of experiment)
Hydrogenated isotropic and pyrolytic and nanostructured graphite (Nechaev, 2010)	3.77 ± 0.05 [analysis, process IV, models "C", "D" (Figure 4)]		3.8 ± 0.5 (analysis, process IV)	There are empirical values in the work (analysis of experiment)

local sp^3 -like hybridization, without the diamond-like strong distortion of the graphene network, may be manifested itself in the cases of hydrogen atoms dissolved between graphene layers in isotropic graphite, graphite nanofibers (GNFs) and nanostructured graphite, where obviously there is a situation similar (in a definite degree) to one of the rigidly fixed graphene membranes. As far as we know, it has not been taken into account in many recent theoretical studies.

In this connection, it is expedient to note that there are a number of theoretical works showing

that hydrogen chemisorption corrugates the graphene sheet in fullerene, carbon nanotubes, graphite and graphene, and transforms them from a semimetal into a semiconductor (Sofa et al., 2007; Elias et al., 2009). This can even induce magnetic moments (Yazyev and Helm, 2007; Lehtinen et al., 2004; Boukhvalov et al., 2008).

Previous theoretical studies suggest that single-side hydrogenation of ideal graphene would be thermodynamically unstable (Boukhvalov et al., 2008; Zhou et al., 2009). Thus, it remains a puzzle why the single-side hydrogenation of epitaxial

graphenes is possible and even reversible, and why the hydrogenated species are stable at room temperatures (Elias et al., 2009; Sessi et al., 2009). This puzzling situation is also considered in the present analytical study.

Xiang et al. (2010) noted that their test calculations show that the barrier for the penetration of a hydrogen atom through the six-member ring of graphene is larger than 2.0 eV. Thus, they believe that it is almost impossible for a hydrogen atom to pass through the six-member ring of graphene at room temperature (from a

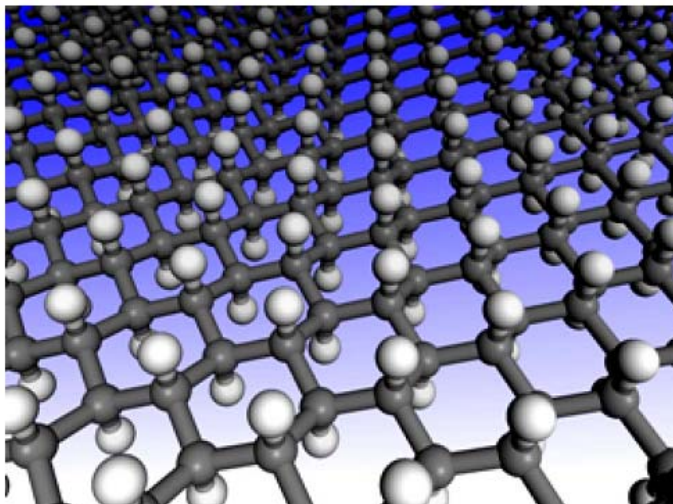


Figure 1. Structure of the theoretical graphane in chair configuration. The carbon atoms are shown in gray and the hydrogen atoms in white. The figure shows the diamond-like distorted hexagonal network with carbon in sp^3 hybridization (Sofa et al., 2007).

private communication with Xiang et al. (2009).

In the present analytical study, a real possibility of the penetration is considered when a hydrogen atom can pass through the graphene network at room temperature. This is the case of existing relevant defects in graphene, that is, grain boundaries, their triple junctions (nodes) and/or vacancies (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011; Koepke et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012). The present study is related to revealing the atomic mechanisms of reversible hydrogenation of epitaxial graphenes, compared with membrane graphenes.

In the next parts of this paper, results of thermodynamic analysis, comparison and interpretation of some theoretical and experimental data are presented, which are related to better understanding and/or solving of the open questions mentioned above. It is related to a further development and modification of our previous analytical results (2010-2014), particularly published in the openaccess journals. Therefore, in the present paper, the related figures 1- 25 from our "open" publication (Nechaev and Veziroglu, 2013) are referred.

CONSIDERATION OF SOME ENERGETIC CHARACTERISTICS OF THEORETICAL GRAPHANES

In the work of Sofa et al. (2007), the stability of graphane, a fully saturated extended two-dimensional hydrocarbon derived from a single grapheme sheet with formula CH,

has been predicted on the basis of the first principles and total-energy calculations. All of the carbon atoms are in sp^3 hybridization forming a hexagonal network (a strongly diamond-like distorted graphene network) and the hydrogen atoms are bonded to carbon on both sides of the plane in an alternative manner. It has been found that graphane can have two favorable conformations: a chair-like (diamond-like, Figure 1) conformer and a boat-like (zigzag-like) conformer (Sofa et al., 2007).

The diamond-like conformer (Figure 1) is more stable than the zigzag-like one. This was concluded from the results of the calculations of binding energy ($\Delta H_{\text{bind. (graphane)}}$) (that is, the difference between the total energy of the isolated atoms and the total energy of the compounds), and the standard energy of formation ($\Delta H_{\text{f298 (graphane)}}^0$) of the compounds ($\text{CH}_{(\text{graphane})}$) from crystalline graphite ($\text{C}_{(\text{graphite})}$) and gaseous molecular hydrogen ($\text{H}_{2(\text{gas})}$) at the standard pressure and temperature conditions (Sofa et al., 2007; Dzhurakhalov and Peeters, 2011).

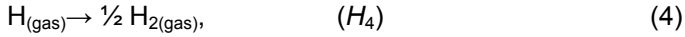
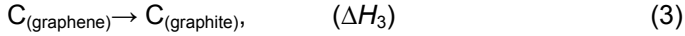
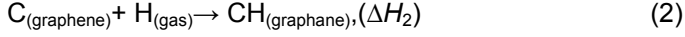
For the diamond-like graphane, the former quantity is $\Delta H_{\text{bind. (graphane)}} = 6.56$ eV/atom, and the latter one is $\Delta H_1 = \Delta H_{\text{f298 (graphane)}}^0 = - 0.15$ eV/atom. The latter quantity corresponds to the following reaction:



Where ΔH_1 is the standard energy (enthalpy) change for this reaction.

By using the theoretical quantity of $\Delta H_{\text{f298 (graphane)}}^0$, one can evaluate, using the framework of the thermodynamic method of cyclic processes (Karapet'yants and

Karapet'yants, 1968; Bazarov, 1976), a value of the energy of formation (ΔH_2) of graphane ($\text{CH}_{(\text{graphane})}$) from graphene ($\text{C}_{(\text{graphene})}$) and gaseous atomic hydrogen ($\text{H}_{(\text{gas})}$). For this, it is necessary to take into consideration the following three additional reactions:



where ΔH_2 , ΔH_3 and ΔH_4 are the standard energy (enthalpy) changes.

Reaction 2 can be presented as a sum of Reactions 1, 3 and 4 using the framework of the thermodynamic method of cyclic processes (Bazarov, 1976):

$$\Delta H_2 = (\Delta H_3 + \Delta H_4 + \Delta H_1). \quad (5)$$

Substituting in Equation 5 the known experimental values (Karapet'yants and Karapet'yants, 1968; Dzhurakhalov and Peeters, 2011) of $\Delta H_4 = -2.26$ eV/atom and $\Delta H_3 = -0.05$ eV/atom, and also the theoretical value (Sofa et al., 2007) of $\Delta H_1 = -0.15$ eV/atom, one can obtain a desired value of $\Delta H_2 = -2.5 \pm 0.1$ eV/atom. The quantity of $-\Delta H_2$ characterizes the breakdown energy of C-H sp^3 bond in graphane (Figure 1), relevant to the breaking away of one hydrogen atom from the material, which is $\Delta H_{(\text{C-H})\text{graphane}} = -\Delta H_2 = 2.5 \pm 0.1$ eV (Table 1A).

In evaluating the above mentioned value of ΔH_3 , one can use the experimental data (Karapet'yants and Karapet'yants, 1968) on the graphite sublimation energy at 298K ($\Delta H_{\text{subl.}(\text{graphite})} = 7.41 \pm 0.05$ eV/atom), and the theoretical data (Dzhurakhalov and Peeters, 2011) on the binding cohesive energy at about 0K for graphene ($\Delta H_{\text{cohes.}(\text{graphene})} = 7.40$ eV/atom). Therefore, neglecting the temperature dependence of these quantities in the interval of 0 to 298K, one obtains the value of $\Delta H_3 \approx -0.05$ eV/atom.

$\Delta H_{\text{cohes.}(\text{graphene})}$ quantity characterizes the breakdown energy of 1.5 C-C sp^2 bond in graphene, relevant to the breaking away of one carbon atom from the material. Consequently, one can evaluate the breakdown energy of C-C sp^2 bonds in graphene, which is $\Delta H_{(\text{C-C})\text{graphene}} = 4.93$ eV. This theoretical quantity coincides with the similar empirical quantities obtained in (Nechaev and Veziroglu, 2013) from $\Delta H_{\text{subl.}(\text{graphite})}$ for C-C sp^2 bonds in graphene and graphite, which are $\Delta H_{(\text{C-C})\text{graphene}} \approx \Delta H_{(\text{C-C})\text{graphite}} = 4.94 \pm 0.03$ eV. The similar empirical quantity for C-C sp^3 bonds in diamond obtained from the diamond sublimation energy $\Delta H_{\text{subl.}(\text{diamond})}$ (Karapet'yants and Karapet'yants, 1968) is $\Delta H_{(\text{C-C})\text{diamond}} = 3.69 \pm 0.02$ eV (Nechaev and Veziroglu, 2013).

It is important to note that chemisorption of hydrogen on graphene was studied (Dzhurakhalov and Peeters, 2011) using atomistic simulations, with a second

generation reactive empirical bond order of Brenner interatomic potential. As shown, the cohesive energy of graphane (CH) in the ground state is $\Delta H_{\text{cohes.}(\text{graphane})} = 5.03$ eV/atom (C). This results in the binding energy of hydrogen, which is $\Delta H_{(\text{C-H})\text{graphane}} = 1.50$ eV/atom (Dzhurakhalov and Peeters, 2011) (Table 1A).

The theoretical $\Delta H_{\text{bind.}(\text{graphane})}$ quantity characterizes the breakdown energy of one C-H sp^3 bond and 1.5 C-C sp^3 bonds (Figure 1). Hence, by using the above mentioned values of $\Delta H_{\text{bind.}(\text{graphane})}$ and $\Delta H_{(\text{C-H})\text{graphane}}$, one can evaluate the breakdown energy of C-C sp^3 bonds in the theoretical graphane (Sofa et al., 2007), which is $\Delta H_{(\text{C-C})\text{graphane}} = 2.7$ eV (Table 1). Also, by using the above noted theoretical values of $\Delta H_{\text{cohes.}(\text{graphane})}$ and $\Delta H_{(\text{C-H})\text{graphane}}$, one can evaluate similarly the breakdown energy of C-C sp^3 bonds in the theoretical graphane (Dzhurakhalov and Peeters, 2011), which is $\Delta H_{(\text{C-C})\text{graphane}} = 2.35$ eV (Table 1A).

CONSIDERATION AND INTERPRETATION OF THE DATA ON DEHYDROGENATION OF THEORETICAL GRAPHANE, COMPARING WITH THE RELATED EXPERIMENTAL DATA

In Openov and Podlivaev (2010) and Elias et al. (2009) the process of hydrogen thermal desorption (TDS) from graphane has been studied using the method of molecular dynamics. The temperature dependence (for $T = 1300 - 3000\text{K}$) of the time ($t_{0.01}$) of hydrogen desorption onset (that is, the time $t_{0.01}$ of removal $\sim 1\%$ of the initial hydrogen concentration $C_0 \approx 0.5$ (in atomic fractions), $-\Delta C/C_0 \approx 0.01$, $C/C_0 \approx 0.99$) from the $\text{C}_{54}\text{H}_{7(54+18)}$ clustered with 18 hydrogen passivating atoms at the edges to saturate the dangling bonds of sp^3 -hybridized carbon atoms have been calculated. The corresponding activation energy of $\Delta H_{(\text{des.})} = E_a = 2.46 \pm 0.17$ eV and the corresponding (temperature independent) frequency factor $A = (2.1 \pm 0.5) \times 10^{17} \text{ s}^{-1}$ have also been calculated. The process of hydrogen desorption at $T = 1300 - 3000\text{K}$ has been described in terms of the Arrhenius-type relationship:

$$1/t_{0.01} = A \exp(-E_a/k_B T), \quad (6)$$

where k_B is the Boltzmann constant.

Openov and Podlivaev (2010) predicted that their results would not contradict the experimental data (Elias et al., 2009), according to which the nearly complete desorption of hydrogen ($-\Delta C/C_0 \approx 0.9$, $C/C_0 \approx 0.1$) from a free-standing graphane membrane (Figure 2B) was achieved by annealing it in argon at $T = 723\text{K}$ for 24 h (that is, $t_{0.9(\text{membr. [5]) } 723\text{K}} = 8.6 \times 10^4 \text{ s}$). However, as the analysis presented below shows, this declaration (Openov and Podlivaev, 2010) is not enough adequate.

By using Equation (6), Openov and Podlivaev, 2010) evaluated the quantity of $t_{0.01(\text{graphane}[4])}$ for $T = 300\text{K}$

($\sim 1 \cdot 10^{24}$ s) and for $T = 600\text{K}$ ($\sim 2 \times 10^3$ s). However, they noted that the above two values of $t_{0.01(\text{graphane})}$ should be considered as rough estimates. Indeed, using Equation 6, one can evaluate the value of $t_{0.01(\text{graphane}[4])723\text{K}} \approx 0.7$ s for $T = 723\text{K}$, which is much less (by five orders) than the $t_{0.9(\text{membr.}[5])723\text{K}}$ value in Elias et al. (2009).

In the framework of the formal kinetics approximation in the first order rate reaction (Bazarov, 1976) a characteristic quantity for the reaction of hydrogen desorption is $\tau_{0.63}$ - the time of the removal of $\sim 63\%$ of the initial hydrogen concentration C_0 (that is, $-\Delta C/C_0 \approx 0.63$, $C/C_0 \approx 0.37$) from the hydrogenated graphene. Such a first order rate reaction (desorption) can be described by the following equations (Nechaev, 2010; Nechaev and Veziroglu, 2013; Bazarov, 1976):

$$dC / dt = -KC, \quad (7)$$

$$(C / C_0) = \exp(-Kt) = \exp(-t / \tau_{0.63}), \quad (8)$$

$$K = (1 / \tau_{0.63}) = K_0 \exp(-\Delta H_{\text{des.}} / k_B T), \quad (9)$$

Where C is the averaged concentration at the annealing time t , $K = (1 / \tau_{0.63})$ is the reaction (desorption) rate constant, $\Delta H_{\text{des.}}$ is the reaction (desorption) activation energy, and K_0 , the per-exponential (or frequency) factor of the reaction rate constant.

In the case of a diffusion rate limiting kinetics, the quantity of K_0 is related to a solution of the corresponding diffusion problem ($K_0 \approx D_0 / L^2$, where D_0 is the per-exponential factor of the diffusion coefficient, L is the characteristic diffusion length) (Nechaev, 2010; Nechaev and Veziroglu, 2013).

In the case of a non-diffusion rate limiting kinetics, which is obviously related to the situation of Openov and Podlivaev (2010) and Elias et al. (2009), the quantity of K_0 may be the corresponding vibration (for (C-H) bonds) frequency ($K_0 = \nu_{(\text{C-H})}$), the quantity $\Delta H_{(\text{des.})} = \Delta H_{(\text{C-H})}$ (Table 1), and Equation (9) corresponds to Polanyi-Wigner (Nechaev, 2010; Nechaev and Veziroglu, 2013).

By substituting in Equation (8) the quantities of $t = t_{0.01(\text{graphane}[4])723\text{K}}$ and $(C/C_0) = 0.99$, one can evaluate the desired quantity $\tau_{0.63(\text{graphane}[4])723\text{K}} \approx 70$ s. Analogically, the quantity of $t_{0.9(\text{graphane}[4])723\text{K}} \approx 160$ s can be evaluated, which is less by about three orders - than the experimental value (Elias et al., 2009) of $t_{0.9(\text{membr.}[5])723\text{K}}$. In the same manner, one can evaluate the desired quantity $\tau_{0.63(\text{membr.}[5])723\text{K}} \approx 3.8 \times 10^4$ s, which is higher (by about three orders) than $\tau_{0.63(\text{graphane}[4])723\text{K}}$.

By using Equation (9) and supposing that $\Delta H_{\text{des.}} = E_a$ and $K = 1 / \tau_{0.63(\text{graphane}[4])723\text{K}}$, one can evaluate the analytical quantity of $K_{0(\text{graphane}[4])} = 2 \times 10^{15} \text{ s}^{-1}$ for graphane of (Openov and Podlivaev, 2010) (Table 1A).

By substituting in Equation (9) the quantity of $K = K_{(\text{membr.}[5])723\text{K}} = 1 / \tau_{0.63(\text{membr.}[5])723\text{K}}$ and supposing that $\Delta H_{\text{des.}(\text{membr.}[5])} \approx \Delta H_{\text{C-H}(\text{graphane}[3,4])} \approx 2.5 \text{ eV}$ (Sofa et al.,

2007; Nechaev and Veziroglu, 2013; Openov and Podlivaev, 2010) (Table 1A), one can evaluate the quantity of $K_{0(\text{membr.}[5])} = \nu_{(\text{membr.}[5])} \approx 7 \times 10^{12} \text{ s}^{-1}$ for the experimental graphane membranes of Elias et al. (2009). The obtained quantity of $\nu_{(\text{membr.}[5])}$ is less by one and a half orders of the vibrational frequency $\nu_{\text{RD}} = 2.5 \times 10^{14} \text{ s}^{-1}$, corresponding to the D Raman peak (1342 cm^{-1}) for hydrogenated graphene membrane and epitaxial graphene on SiO_2 (Figure 2). The activation of the D Raman peak in the hydrogenated samples authors (Elias et al., 2009) attribute to breaking of the translation symmetry of C-C sp^2 bonds after formation of C-H sp^3 bonds.

The quantity $\nu_{(\text{membr.}[5])}$ is less by one order of the value (Xie et al., 2011) of the vibration frequency $\nu_{\text{HREELS}} = 8.7 \times 10^{13} \text{ s}^{-1}$ corresponding to an additional HREELS peak arising from C-H sp^3 hybridization; a stretching appears at 369 meV after a partial hydrogenation of the epitaxial graphene. Xie et al. (2011) suppose that this peak can be assigned to the vertical C-H bonding, giving direct evidence for hydrogen attachment on the epitaxial graphene surface.

Taking into account ν_{RD} and ν_{HREELS} quantities, and substituting in Equation (9) quantities of $K = 1 / \tau_{0.63(\text{membr.}[5])723\text{K}}$ and $K_0 \approx K_{0(\text{membr.}[5])} \approx \nu_{\text{HREELS}}$, one can evaluate $\Delta H_{\text{des.}(\text{membr.}[5])} = \Delta H_{\text{C-H}(\text{membr.}[5])} \approx 2.66 \text{ eV}$ (Table 1A). In such approximation, the obtained value of $\Delta H_{\text{C-H}(\text{membr.}[5])}$ coincides (within the errors) with the experimental value (Pimenova et al., 2002) of the breakdown energy of C-H bonds in hydrofullerene $\text{C}_{60}\text{H}_{36}$ ($\Delta H_{\text{C-H}(\text{C}_{60}\text{H}_{36})} = 2.64 \pm 0.01 \text{ eV}$, Table 1B).

The above analysis of the related data shows that the experimental graphene membranes (hydrogenated up to the near-saturation) can be used. The following thermodesorption characteristics of the empirical character, relevant to Equation (9): $\Delta H_{\text{des.}(\text{membr.}[5])} = \Delta H_{\text{C-H}(\text{membr.}[5])} = 2.6 \pm 0.1 \text{ eV}$, $K_{0(\text{membr.}[5])} = \nu_{\text{C-H}(\text{membr.}[5])} \approx 5 \times 10^{13} \text{ s}^{-1}$ (Table 1A). The analysis also shows that this is a case for a non-diffusion rate limiting kinetics, when Equation (9) corresponds to Polanyi-Wigner (Nechaev, 2010; Nechaev and Veziroglu, 2013). Certainly, these tentative results could be directly confirmed and/or modified by receiving and treating within Equations (8) and (9) of the experimental data on $\tau_{0.63}$ at several annealing temperatures.

The above noted fact that the empirical (Elias et al., 2009; Nechaev and Veziroglu, 2013) quantity $\tau_{0.63(\text{membr.}[5])723\text{K}}$ is much larger (by about 3 orders), than the theoretical (Openov and Podlivaev, 2010; Nechaev and Veziroglu, 2013) one ($\tau_{0.63(\text{graphane}[4])723\text{K}}$), is consistent with that mentioned in (Elias et al., 2009). The alternative possibility has been supposed in Elias et al., (2009) that (i) the experimental graphane membrane (a free-standing one) may have "a more complex hydrogen bonding, than the suggested by the theory", and that (ii) graphane (CH) (Sofa et al., 2007) may be until now the theoretical material.

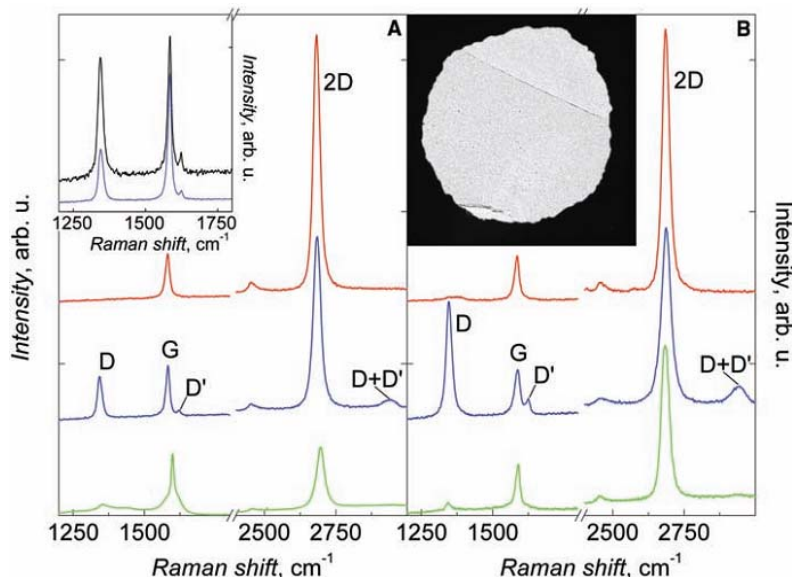


Figure 2. Changes in Raman spectra of graphene caused by hydrogenation (Elias et al., 2009). The spectra are normalized to have a similar integrated intensity of the G peak. (A) Graphene on SiO₂. (B) Free-standing graphene. Red, blue, and green curves (top to bottom) correspond to pristine, hydrogenated, and annealed samples, respectively. Graphene was hydrogenated for ~2 hours, and the spectra were measured with a Renishaw spectrometer at wavelength 514 nm and low power to avoid damage to the graphene during measurements. (Left inset) Comparison between the evolution of D and D' peaks for single- and double-sided exposure to atomic hydrogen. Shown is a partially hydrogenated state achieved after 1 hour of simultaneous exposure of graphene on SiO₂ (blue curve) and of a membrane (black curve). (Right inset) TEM image of one of the membranes that partially covers the aperture 50 μm in diameter.

CONSIDERATION OF THE EXPERIMENTAL DATA ON HYDROGENATION-DEHYDROGENATION OF MONO- AND BI-LAYER EPITAXIAL GRAPHENES, AND COMPARING THE RELATED DATA FOR FREE-STANDING GRAPHENE

Characteristics of hydrogenation-dehydrogenation of mono-layer epitaxial graphenes

In Elias et al. (2009), both the graphene membrane samples considered above, and the epitaxial graphene and bi-graphene samples on substrate SiO₂ were exposed to cold hydrogen DC plasma for 2 h to reach the saturation in the measured characteristics. They used a low-pressure (0.1 mbar) hydrogen-argon mixture of 10% H₂. Raman spectra for hydrogenated and subsequently annealed free-standing graphene membranes (Figure 2B) are rather similar to those for epitaxial graphene samples (Figure 2A), but with some notable differences. If hydrogenated simultaneously for 1 h, and before reaching the saturation (a partial hydrogenation), the D peak area for a free-standing membrane is two factors greater than the area for graphene on a substrate (Figure 2, the left inset). This indicates the formation of twice as

many C-H sp^3 bonds in the membrane. This result also agrees with the general expectation that atomic hydrogen attaches to both sides of the membranes. Moreover, the D peak area became up to about three times greater than the G peak area after prolonged exposures (for 2 h, a near-complete hydrogenation) of the membranes to atomic hydrogen.

The integrated intensity area of the D peak in Figure 2B corresponding to the adsorbed hydrogen saturation concentration in the graphene membranes is larger by a factor of about 3 for the area of the D peak in Figure 2A, corresponding to the hydrogen concentration in the epitaxial graphene samples.

The above noted Raman spectroscopy data (Elias et al., 2009) on dependence of the concentration (C) of adsorbed hydrogen from the hydrogenation time (t) (obviously, at about 300K) can be described with Equation (8) (Xiang et al., 2010; Bazarov, 1976). By using the above noted Raman spectroscopy data (Elias et al., 2009) (Figure 2), one can suppose that the near-saturation ($(C/C_0) \approx 0.95$) time ($t_{0.95}$) for the free standing graphene membranes (at ~300K) is about 3 h, and a maximum possible (but not defined experimentally) value of $C_{0(\text{membr.})} \approx 0.5$ (atomic fraction, that is, the atomic ratio

(H/C) = 1). Hence, using Equation (8)* results in the quantities of $\tau_{0.63(\text{membr.}[5])\text{hydr.}300\text{K}} \approx 1.0$ h, $C_{3\text{h}(\text{membr.}[5])} \approx 0.475$, $C_{2\text{h}(\text{membr.}[5])} \approx 0.43$ and $C_{1\text{h}(\text{membr.}[5])} \approx 0.32$, where, $C_{3\text{h}(\text{membr.}[5])}$, $C_{2\text{h}(\text{membr.}[5])}$ and $C_{1\text{h}(\text{membr.}[5])}$ being the adsorbed hydrogen concentration at the hydrogenation time (t) equal to 3, 2 and 1 h, respectively. It is expedient to note that the quantity of $C_{0(\text{membr.}[5])} \approx 0.5$ corresponds to the local concentration of $C_{0(\text{membr.}[5])\text{one_side}} \approx 0.33$ for each of the two sides of a membrane, that is, the local atomic ratio (H/C) = 0.50.

The evaluated value of $\tau_{0.63(\text{membr.}[5])\text{hydr.}300\text{K}}$ (for process of hydrogenation of the free standing graphene membranes (Elias et al., 2009) is much less (by about 26 orders) of the evaluated value of the similar quantity of $\tau_{0.63(\text{membr.}[5])\text{dehydr.}300\text{K}} \approx (0.4 - 2.7) \times 10^{26}$ h (if $\Delta H_{(\text{des.})} = (2.49 - 2.61)$ eV, $K_{0(\text{des.})} = (0.7 - 5) \times 10^{13}$ s⁻¹, Table 1A) for process of dehydrogenation of the same free standing graphene membranes (Elias et al., 2009). This shows that the activation energy of the hydrogen adsorption ($\Delta H_{(\text{ads.})}$) for the free standing graphene membranes (Elias et al., 2009) is considerably less than the activation energy of the hydrogen desorption ($\Delta H_{(\text{des.})} = (2.5$ or $2.6)$ eV). Hence, by using Equation (9) and supposing that $K_{0(\text{ads.})} \approx K_{0(\text{des.})}$, one can obtain a reasonable value of $\Delta H_{(\text{ads.})\text{membr.}[5]} = 1.0 \pm 0.2$ eV (Table 1). The heat of adsorption of atomic hydrogen by the free standing graphene membranes (Elias et al., 2009) may be evaluated as (Nechaev, 2010; Bazarov, 1976): $(\Delta H_{(\text{ads.})\text{membr.}[5]} - \Delta H_{(\text{des.})\text{membr.}[5]}) = -1.5 \pm 0.2$ eV (an exothermic reaction).

One can also suppose that the near-saturation ((C/C₀) ≈ 0.95) time ($t_{0.95}$) for the epitaxial graphene samples (at ~300K) is about 2 h. Hence, by using Equation 8 and the above noted data (Elias et al., 2009) on the relative concentrations [$(C_{1\text{h}(\text{membr.}[5])} / C_{1\text{h}(\text{epitax.}[5])}) \approx 2$, and $(C_{3\text{h}(\text{membr.}[5])} / C_{3\text{h}(\text{epitax.}[5])}) \approx 3$], one can evaluate the quantities of $\tau_{0.63(\text{epitax.}[5])\text{hydr.}300\text{K}} \approx 0.7$ h and $C_{0(\text{epitax.}[5])} \approx 0.16$. Obviously, $C_{0(\text{epitax.}[5])}$ is related only for one of the two sides of an epitaxial graphene layer, and the local atomic ratio is (H/C) ≈ 0.19. It is considerably less (about 2.6 times) of the above considered local atomic ratio (H/C) = 0.5 for each of two sides the free standing hydrogenated graphene membranes.

The obtained value of $\tau_{0.63(\text{epitax.}[5])\text{hydr.}300\text{K}} \approx 0.7$ h (for process of hydrogenation of the epitaxial graphene samples (Elias et al., 2009) is much less (by about two - seven orders) of the evaluated values of the similar quantity for the process of dehydrogenation of the same epitaxial graphene samples (Elias et al., 2009) ($\tau_{0.63(\text{epitax.}[5])\text{dehydr.}300\text{K}} \approx (1.5 \times 10^2 - 1.0 \times 10^7)$ h, for $\Delta H_{(\text{des.})} = (0.3 - 0.9)$ eV and $K_{0(\text{des.})} = (0.2 - 3.5 \times 10^4)$ s⁻¹, Table 1A). Hence, by using Equation 9 and supposing that $K_{0(\text{ads.})} \approx K_{0(\text{des.})}$ (a rough approximation), one can obtain a reasonable value of $\Delta H_{(\text{ads.})\text{epitax.}[5]} \approx 0.3 \pm 0.2$ eV (Table 1A). The heat of adsorption of atomic hydrogen by the free standing graphene membranes (Elias et al., 2009) may be evaluated as (Nechaev, 2010; Bazarov, 1976):

$(\Delta H_{(\text{ads.})\text{epitax.}[5]} - \Delta H_{(\text{des.})\text{epitax.}[5]}) = -0.3 \pm 0.2$ eV (an exothermic reaction).

The smaller values of $C_{0(\text{epitax.}[5])} \approx 0.16$ and $(\text{H/C})_{(\text{epitax.}[5])} \approx 0.19$ (in comparison with $C_{0(\text{membr.}[5])\text{one_side}} \approx 0.33$ and $(\text{H/C})_{(\text{membr.}[5])\text{one_side}} \approx 0.50$) may point to a partial hydrogenation localized in some defected nanoregions (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011; Koepke et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012) for the epitaxial graphene samples (even after their prolonged (3 h) exposures, that is, after reaching their near-saturation. Similar analytical results, relevance to some other epitaxial graphenes are also presented.

Characteristics of dehydrogenation of mono-layer epitaxial graphenes

According to a private communication from D.C. Elias, a near-complete desorption of hydrogen ($-\Delta C/C_0 \approx 0.95$) from a hydrogenated epitaxial graphene on a substrate SiO₂ (Figure 2A) has been achieved by annealing it in 90% Ar/10% H₂ mixture at $T = 573\text{K}$ for 2 h (that is, $t_{0.95(\text{epitax.}[5])573\text{K}} = 7.2 \times 10^3$ s). Hence, by using Equation 8, one can evaluate the value of $\tau_{0.63(\text{epitax.}[5])573\text{K}} = 2.4 \times 10^3$ s for the epitaxial graphene (Elias et al., 2009), which is about six orders less than the evaluated value of $\tau_{0.63(\text{membr.}[5])573\text{K}} = 1.5 \times 10^9$ s for the free-standing membranes (Elias et al., 2009).

The changes in Raman spectra of graphene (Elias et al., 2009) caused by hydrogenation were rather similar in respect to locations of D, G, D', 2D and (D+D') peaks, both for the epitaxial graphene on SiO₂ and for the free-standing graphene membrane (Figure 2). Hence, one can suppose that $K_{0(\text{epitax.}[5])} = \nu_{\text{C-H}(\text{epitax.}[5])} \approx K_{0(\text{membr.}[5])} = \nu_{\text{C-H}(\text{membr.}[5])} \approx (0.7$ or $5) \times 10^{13}$ s⁻¹ (Table 1A). Then, by substituting in Equation 9 the values of $K = K_{(\text{epitax.}[5])573\text{K}} = 1/\tau_{0.63(\text{epitax.}[5])573\text{K}}$ and $K_0 \approx K_{0(\text{epitax.}[5])} \approx K_{0(\text{membr.}[5])}$, one can evaluate $\Delta H_{(\text{des.})\text{epitax.}[5]} = \Delta H_{\text{C-H}(\text{epitax.}[5])} \approx (1.84$ or $1.94)$ eV (Table 1A). Here, the case is supposed of a non-diffusion-rate-limiting kinetics, when Equation 9 corresponds to the Polanyi-Wigner one (Nechaev, 2010). Certainly, these tentative thermodynamic characteristics of the hydrogenated epitaxial graphene on a substrate SiO₂ could be directly confirmed and/or modified by further experimental data on $\tau_{0.63(\text{epitax.})}$ at various annealing temperatures.

It is easy to show that: 1) these analytical results (for the epitaxial graphene (Elias et al., 2009) are not consistent with the presented below analytical results for the mass spectrometry data (Figure 3, TDS peaks ## 1-3, Table 1A) on TDS of hydrogen from a specially prepared single-side (obviously, epitaxial*) graphene (Elias et al., 2009); and 2) they cannot be described in the framework of the theoretical models and characteristics of thermal

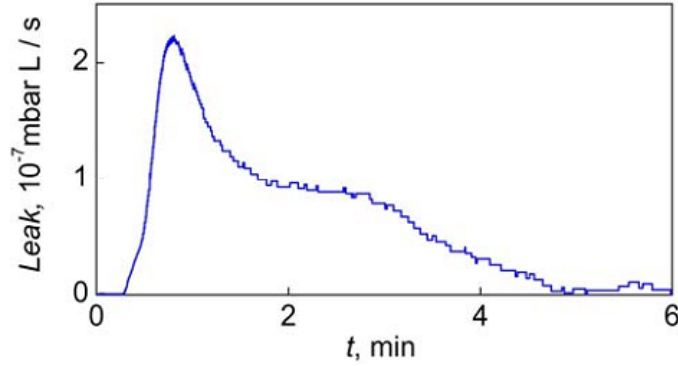


Figure 3. Desorption of hydrogen from single-side graphane (Elias et al., 2009). The measurements were done by using a leak detector tuned to sense molecular hydrogen. The sample was heated to 573 K (the heater was switched on at $t = 10$ s). Control samples (exposed to pure argon plasma) exhibited much weaker and featureless response ($< 5 \cdot 10^{-6}$ mbar L/s), which is attributed to desorption of water at heated surfaces and subtracted from the shown data (water molecules are ionized in the mass-spectrometer, which also gives rise to a small hydrogen signal).

stability of SSHG (Openov and Podlivaev, 2012) or graphane (Podlivaev and Openov, 2011).

According to further consideration presented below (both here and subsequently), the epitaxial graphene case (Elias et al., 2009) may be related to a hydrogen desorption case of a diffusion rate limiting kinetics, when $K_0 \neq v$, and Equation (9) does not correspond to the Polanyi-Wigner one (Nechaev, 2010).

By using the method of Nechaev, (2010) of treatment from the TDS spectra, relevant to the mass spectrometry data (Elias et al., 2009) (Figure 3) on TDS of hydrogen from the specially prepared single-side (epitaxial*) graphane (under heating from room temperature to 573K for 6 min), one can obtain the following tentative results:

- (1) The total integrated area of the TDS spectra corresponds to $\sim 10^{-8}$ g of desorbed hydrogen that may correlate with the graphene layer mass (unfortunately, it's not considered in Elias et al. (2009), particularly, for evaluation of the C_0 quantities);
- (2) The TDS spectra can be approximated by three thermodesorption (TDS) peaks (# # 1-3);
- (3) TDS peak # 1 (~ 30 % of the total area, $T_{\max\#1} \approx 370$ K) can be characterized by the activation energy of $\Delta H_{(\text{des.})} = E_{\text{TDS-peak \# 1}} = 0.6 \pm 0.3$ eV and by the per-exponential factor of the reaction rate constant $K_{0(\text{TDS-peak \# 1})} \approx 2 \cdot 10^7 \text{ s}^{-1}$;
- (4) TDS peak # 2 ($\sim 15\%$ of the total area, $T_{\max\#2} \approx 445\text{K}$) can be characterized by the activation energy $\Delta H_{(\text{des.})} = E_{\text{TDS-peak \# 2}} = 0.6 \pm 0.3$ eV, and by the per-exponential factor of the reaction rate constant $K_{0(\text{TDS-peak \# 2})} \approx 1 \times 10^6 \text{ s}^{-1}$;
- (5) TDS peak # 3 ($\sim 55\%$ of the total area, $T_{\max\#3} \approx 540\text{K}$) can be characterized by the activation energy $\Delta H_{(\text{des.})} =$

$E_{\text{TDS-peak \# 3}} = 0.23 \pm 0.05$ eV and by the per-exponential factor of the reaction rate constant $K_{0(\text{TDS-peak \# 3})} \approx 2.4 \text{ s}^{-1}$.

These analytical results (on quantities of $\Delta H_{(\text{des.})}$ and K_0) show that all three of the above noted TDS processes (#1_{TDS}, #2_{TDS} and #3_{TDS}) can not be described in the framework of the Polanyi-Wigner equation (Nechaev, 2010; Nechaev and Veziroglu, 2013) (due to the obtained low values of the $K_{0(\text{des.})}$ and $\Delta H_{(\text{des.})}$ quantities, in comparison with the $v_{(\text{C-H})}$ and $\Delta H_{(\text{C-H})}$ ones).

As shown below, these results may be related to a hydrogen desorption case of a diffusion-rate-limiting kinetics (Nechaev, 2010; Nechaev and Veziroglu, 2013), when in Equation (9) the value of $K_0 \approx D_{0\text{app.}} / L^2$ and the value of $\Delta H_{\text{des.}} = Q_{\text{app.}}$, where $D_{0\text{app.}}$ is the per-exponent factor of the apparent diffusion coefficient $D_{\text{app.}} = D_{0\text{app.}} \exp(-Q_{\text{app.}}/k_B T)$, $Q_{\text{app.}}$ is the apparent diffusion activation energy, and L is the characteristic diffusion size (length), which (as shown below) may correlate with the sample diameter (Elias et al., 2009) ($L \sim d_{\text{sample}} \approx 4 \times 10^{-3}$ cm, Figure 2, Right inset).

TDS process (or peak) #3_{TDS} (Figure 3, Table 1A) may be related to the diffusion-rate-limiting TDS process (or peak) I in (Nechaev, 2010), for which the apparent diffusion activation energy is $Q_{\text{app.I}} \approx 0.2$ eV $\approx E_{\text{TDS-peak\#3}}$ and $D_{0\text{app.I}} \approx 3 \times 10^{-3} \text{ cm}^2/\text{s}$, and which is related to chemisorption models "F" and/or "G" (Figure 4).

By supposing of $L \sim d_{\text{sample}}$, that is, of the order of diameter of the epitaxial graphene specimens (Elias et al., 2009), one can evaluate the quantity of $D_{0\text{app.}}(\text{TDS-peak\#3}) \approx L^2 \cdot K_{0(\text{TDS-peak\#3})} \approx 4 \times 10^{-5} \text{ cm}$ (or within the errors limit, it is of $(1.3 - 11) \times 10^{-5} \text{ cm}$, for $E_{\text{TDS-peak \# 3}}$ values 0.18 - 0.28 eV, Table 1A). The obtained values of

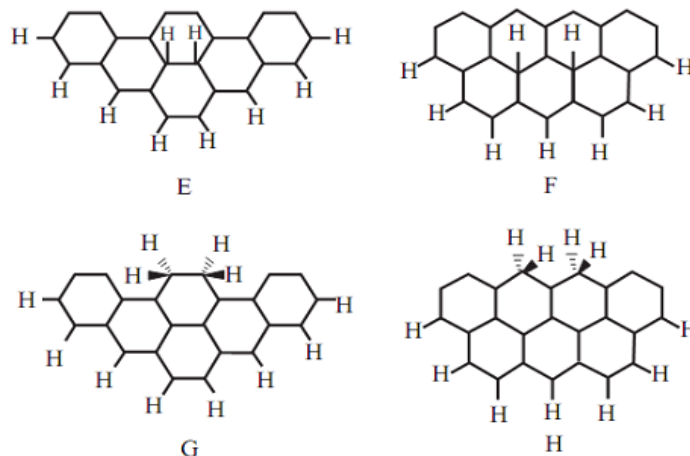


Figure 4. Schematics of some theoretical models (*ab initio* molecular orbital calculations (Yang and Yang, 2002) of chemisorption of atomic hydrogen on graphite on the basal and edge planes.

$D_{0app.(TDS-peak\#3)}$ satisfactory (within one-two orders, that may be within the errors limit) correlate with the $D_{0app.I}$ quantity. Thus, the above analysis shows that for TDS process (or peak) # 3_{TDS} (Elias et al., 2009), the quantity of L may be of the order of diameter (d_{sample}) of the epitaxial* graphene samples.

Within approach (Nechaev, 2010), model “F” (Figure 4) is related to a “dissociative-associative” chemisorption of molecular hydrogen on free surfaces of graphene layers of the epitaxial samples (Elias et al., 2009). Model “G” (Figure 4) is related, within (Nechaev, 2010) approach, to a “dissociative-associative” chemisorption of molecular hydrogen on definite defects in graphene layers of the epitaxial samples (Elias et al., 2009), for instance, vacancies, grain boundaries (domains) and/or triple junctions (nodes) of the grain-boundary network (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011; Koepke et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012), where the dangling carbon bonds can occur.

TDS processes (or peaks) #1_{TDS} and #2_{TDS} (Elias et al., 2009) (Table 1A) may be (in some extent) related to the diffusion-rate-limiting TDS processes (or peaks) I and II in (Nechaev, 2010).

Process II is characterized by the apparent diffusion activation energy $Q_{app.II} \approx 1.2$ eV (that is considerably higher of quantities of $E_{TDS-peak\#1}$ and $E_{TDS-peak\#2}$) and $D_{0app.II} \approx 1.8 \cdot 10^3$ cm²/s. It is related to chemisorption model “H” (Figure 4). Within approach (Nechaev, 2010), model “H” is related (as and model “G”) to a “dissociative - associative” chemisorption of molecular hydrogen on definite defects in graphene layers of the epitaxial samples (Elias et al., 2009), for instance, vacancies, grain boundaries (domains) and/or triple junctions (nodes) of the grain-boundary network noted above,

where the dangling carbon bonds can occur.

By supposing the possible values of $E_{TDS-peaks\#1,2} = 0.3, 0.6$ or 0.9 eV, one can evaluate the quantities of $K_{0(TDS-peak\#1)}$ and $K_{0(TDS-peak\#2)}$ (Table 1A). Hence, by supposing of $L \sim d_{sample}$, one can evaluate the quantities of $D_{0app.(TDS-peak\#1)}$ and $D_{0app.(TDS-peak\#2)}$, some of them correlate with the $D_{0app.I}$ quantity or with $D_{0app.II}$ quantity. It shows that for TDS processes (or peaks) #1_{TDS} and #2_{TDS} (Elias et al., 2009), the quantity of L may be of the order of diameter of the epitaxial* graphene samples.

For the epitaxial graphene (Elias et al., 2009) case, supposing the values of $\Delta H_{des.(epitax.[5])} \approx 0.3, 0.6$ or 0.9 eV results in relevant values of $K_{0(epitax.[5])}$ (Table 1A). Hence, by supposing of $L \sim d_{sample}$, one can evaluate the quantities of $D_{0app.(epitax.[5])}$, some of them correlate with the $D_{0app.I}$ quantity or with $D_{0app.II}$ quantity. It shows that for these two processes, the quantity of L also may be of the order of diameter of the epitaxial graphene samples (Elias et al., 2009).

It is important to note that chemisorption of atomic hydrogen with free-standing graphane-like membranes (Elias et al., 2009) and with the theoretical graphanes may be related to model “F” considered in (Nechaev, 2010). Unlike model “F” (Figure 4), where two hydrogen atoms are adsorbed by two alternated carbon atoms in a graphene-like network, in model “F*” a single hydrogen atom is adsorbed by one of the carbon atoms (in the graphene-like network) possessing of 3 unoccupied (by hydrogen) nearest carbons. Model “F*” is characterized (Nechaev, 2010) by the quantity of $\Delta H_{(C-H)F^*} \approx 2.5$ eV, which coincides (within the errors) with the similar quantities ($\Delta H_{(C-H)}$) for graphanes (Table 1A). As also shown in the previous paper parts, the dehydrogenation processes in graphanes (Elias et al., 2009; Openov and Podlivaev, 2010) may be the case of a non-diffusion rate limiting kinetics, for which the quantity of K_0 is the

corresponding vibration frequency ($K_0 = \nu$), and Equation (9) is correspond to the Polanyi-Wigner one.

On the other hand, model “F*” is manifested in the diffusion-rate-limiting TDS process (or peak) III in (Nechaev, 2010) (Table 1B), for which the apparent diffusion activation energy is $Q_{app.III} \approx 2.6 \text{ eV} \approx \Delta H_{(C-H)^*F^*}$ and $D_{0app.III} \approx 3 \times 10^{-3} \text{ cm}^2/\text{s}$. Process III is relevant to a dissociative chemisorption of molecular hydrogen between graphene-like layers in graphite materials (isotropic graphite and nanostructured one) and nanomaterials – GNFs (Nechaev, 2010) (Table 1B).

It is expedient also to note about models “C” and “D”, those manifested in the diffusion-rate-limiting TDS process (or peak) IV in (Nechaev, 2010) (Table 1B), for which the apparent diffusion activation energy is $Q_{app.IV} \approx 3.8 \text{ eV} \approx \Delta H_{(C-H)^*C^*,D^*}$ and $D_{0app.IV} \approx 6 \times 10^2 \text{ cm}^2/\text{s}$. Process IV is relevant to a dissociative chemisorption of molecular hydrogen in defected regions in graphite materials (isotropic graphite, pyrolytic graphane and nanostructured one) (Nechaev, 2010) (Table 1B).

But such processes (III and IV) have not manifested, when the TDS annealing of the hydrogenated epitaxial graphene samples (Elias et al., 2009) (Figure 3), unlike some hydrogen sorption processes in epitaxial graphenes and graphite samples considered in some next parts of this paper.

An interpretation of characteristics of hydrogenation-dehydrogenation of mono-layer epitaxial graphenes

The above obtained values (Table 1A and B) of characteristics of dehydrogenation of mono-layer epitaxial graphene samples (Elias et al., 2009) can be presented as follows: $\Delta H_{des.} \sim Q_{app.I}$ or $\sim Q_{app.II}$ (Nechaev, 2010), $K_{0(des.)} \sim (D_{0app.I} / L^2)$ or $\sim (D_{0app.II} / L^2)$ (Nechaev, 2010), $L \sim d_{sample}$, that is, being of the order of diameter of the epitaxial graphene samples. And it is related to the chemisorption models “F”, “G” and/or “H” (Figure 4).

These characteristics unambiguously point that in the epitaxial graphene samples (Elias et al., 2009), there are the rate-limiting processes (types of I and/or II (Nechaev, 2010) of diffusion of hydrogen, mainly, from chemisorption “centers” [of “F”, “G” and/or “H” types (Figure 4)] localized on the internal graphene surfaces (and/or in the graphene/substrate interfaces) to the frontier edges of the samples. It corresponds to the characteristic diffusion length ($L \sim d_{sample}$) of the order of diameter of the epitaxial graphene samples, which, obviously, cannot be manifested for a case of hydrogen desorption processes from the external graphene surfaces. Such interpretation is direct opposite, relevance to the interpretation of Elias et al. (2009) and a number of others, those probably believe in occurrence of hydrogen desorption processes, mainly, from the external epitaxial graphene surfaces. Such different (in some sense, extraordinary) interpretation is consisted with the above

analytical data (Table 1A) on activation energies of hydrogen adsorption for the epitaxial graphene samples ($\Delta H_{(ads.)epitax.[5]} \approx 0.3 \pm 0.2 \text{ eV}$), which is much less than the similar one for the free standing graphene membranes (Elias et al., 2009) ($\Delta H_{(ads.)membr.[5]} = 1.0 \pm 0.2 \text{ eV}$). It may be understood for the case of chemisorption [of “F”, “G” and/or “H” types (Figure 4)] on the internal graphene surfaces [neighboring to the substrate (SiO_2) surfaces], which obviously proceeds without the diamond-like strong distortion of the graphene network, unlike graphene (Sofa et al., 2007).

Such an extraordinary interpretation is also consisted with the above analytical results about the smaller values of $C_{0(epitax.[5])} \approx 0.16$ and $(H/C)_{(epitax.[5])} \approx 0.19$, in comparison with $C_{0(membr.[5]one_side)} \approx 0.33$ and $(H/C)_{(membr.[5]one_side)} \approx 0.50$. It may point to an “internal” (in the above considered sense) local hydrogenation in the epitaxial graphene layers. It may be, for instance, an “internal” hydrogenation localized, mainly, in some defected nanoregions (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011; Koepke et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012), where their near-saturation may be reached after prolonged (3 h) exposures.

On the basis of the above analytical results, one can suppose that a negligible hydrogen adsorption by the external graphene surfaces (in the epitaxial samples of Elias et al., 2009) is exhibited. Such situation may be due to a much higher rigidity of the epitaxial graphenes (in comparison with the free standing graphene membranes), that may suppress the diamond-like strong distortion of the graphene network attributed for graphene of Sofa et al. (2007). It may result (for the epitaxial graphenes of Elias et al. (2009) in disappearance of the hydrogen chemisorption with characteristics of $\Delta H_{(ads.)membr.[5]}$ and $\Delta H_{(des.)membr.[5]}$ (Table 1A) manifested in the case of the free standing graphene membranes of Elias et al. (2009). And the hydrogen chemisorption with characteristics of $\Delta H_{(ads.)epitax.[5]}$ and $\Delta H_{(des.)epitax.[5]}$ (Table 1A) by the external graphene surfaces, in the epitaxial samples of Elias et al. (2009), is not observed, may be, due to a very fast desorption kinetics, unlike the kinetics in the case of the internal graphene surfaces.

Certainly, such an extraordinary interpretation also needs in a reasonable explanation of results (Figure 2) the fact that the changes in Raman spectra of graphene of Elias et al. (2009) caused by hydrogenation were rather similar with respect to locations of D, G, D', 2D and (D+D') peaks, both for the epitaxial graphene on SiO_2 and for the free-standing graphene membrane.

An interpretation of the data on hydrogenation of bi-layer epitaxial graphenes

In Elias et al. (2009), the same hydrogenation procedures

of the 2 h long expositions have been applied also for bi-layer epitaxial graphene on SiO₂/Si wafer. Bi-layer samples showed little change in their charge carrier mobility and a small D Raman peak, compared to the single-layer epitaxial graphene on SiO₂/Si wafer exposed to the same hydrogenation procedures. Elias et al. (2009) believe that higher rigidity of bi-layers suppressed their rippling, thus reducing the probability of hydrogen adsorption.

But such an interpretation (Elias et al., 2009) does not seem adequate, in order to take into account the above, and below (next parts of this paper) the presented consideration and interpretation of a number of data.

By using the above extraordinary interpretation, and results on characteristics ($Q_{app,III} \approx 2.6$ eV, $D_{0app,III} \approx 3 \times 10^{-3}$ cm²/s (Table 1B) of a rather slow diffusion of atomic hydrogen between neighboring graphene-like layers in graphitic materials and nanostructures (process III, model "F*" (Nechaev, 2010), one can suppose a negligible diffusion penetration of atomic hydrogen between the two graphene layers in the bi-layer epitaxial samples of Elias et al. (2009) (during the hydrogenation procedures of the 2 h long expositions, obviously, at $T \approx 300$ K). Indeed, by using values of $Q_{app,III}$ and $D_{0app,III}$, one can estimate the characteristic diffusion size (length) $L \sim 7 \times 10^{-22}$ cm, which points to absence of such diffusion penetration.

In the next next parts of this study, a further consideration of some other known experimental data on hydrogenation and thermal stability characteristics of mono-layer, bi-layer and three-layer epitaxial graphene systems is given, where (as shown) an important role plays some defects found in graphene networks (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011; Koepke et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012), relevant to the probability of hydrogen adsorption and the permeability of graphene networks for atomic hydrogen.

Consideration and interpretation of the Raman spectroscopy data on hydrogenation-dehydrogenation of graphene flakes, the scanning tunneling microscopy/ scanning tunnelingspectroscopy (STM/STS) data on hydrogenation-dehydrogenation of epitaxial graphene and graphite (HOPG) surfaces and the high-resolution electron energy loss spectroscopy/low-energy electron diffraction (HREELS/LEED) data on dehydrogenation of epitaxial graphene on SiC substrate

In Wojtaszek et al. (2011), it is reported that the hydrogenation of single and bilayer graphene flakes by an argon-hydrogen plasma produced a reactive ion etching (RIE) system. They analyzed two cases: One

where the graphene flakes were electrically insulated from the chamber electrodes by the SiO₂ substrate, and the other where the flakes were in electrical contact with the source electrode (a graphene device). Electronic transport measurements in combination with Raman spectroscopy were used to link the electric mean free path to the optically extracted defect concentration, which is related to the defect distance (L_{def}). This showed that under the chosen plasma conditions, the process does not introduce considerable damage to the graphene sheet, and that a rather partial hydrogenation ($C_H \leq 0.05\%$) occurs primarily due to the hydrogen ions from the plasma, and not due to fragmentation of water adsorbates on the graphene surface by highly accelerated plasma electrons. To quantify the level of hydrogenation, they used the integrated intensity ratio (I_D/I_G) of Raman bands. The hydrogen coverage (C_H) determined from the defect distance (L_{def}) did not exceed $\sim 0.05\%$.

In Nechaev and Veziroglu (2013), the data (Wojtaszek et al., 2011) (Figure 5) has been treated and analyzed. The obtained analytical results (Table 2) on characteristics of hydrogenation-dehydrogenation of graphene flakes (Wojtaszek et al., 2011) may be interpreted within the models used for interpretation of the similar characteristics for the epitaxial graphenes of Elias et al. (2009) (Table 1A), which are also presented (for comparing) in Table 2.

By taking into account the fact that the RIE exposure regime (Wojtaszek et al., 2011) is characterized by a form of $(I_D/I_G) \sim L_{def}^{-2}$ (for $(I_D/I_G) < 2.5$), $L_{def} \approx 11 - 17$ nm and the hydrogen concentration $C_H \leq 5 \times 10^4$, one can suppose that the hydrogen adsorption centers in the single graphene flakes (on the SiO₂ substrate) are related in some point, nanodefects (that is, vacancies and/or triple junctions (nodes) of the grain-boundary network) of diameter $d_{def} \approx \text{const}$. In such a model, the quantity C_H can be described satisfactory as:

$$C_H \approx n_H (d_{def})^2 / (L_{def})^2, \quad (10)$$

Where $n_H \approx \text{const}$. is the number of hydrogen atoms adsorbed by a center; $C_H \sim (I_D/I_G) \sim L_{def}^{-2}$.

It was also found (Wojtaszek et al., 2011) that after the Ar/H₂ plasma exposure, the (I_D/I_G) ratio for bi-layer graphene device is larger than that of the single graphene device. As noted in (Wojtaszek et al. (2011), this observation is in contradiction to the Raman ratios after exposure of graphene to atomic hydrogen and when other defects are introduced. Such a situation may have place in Elias et al. (2009) for bi-layer epitaxial graphene on SiO₂/Si wafer.

In Castellanos-Gomez (2012) and Wojtaszek et al. (2012), the effect of hydrogenation on topography and electronic properties of graphene grown by CVD on top of a nickel surface and HOPG surfaces were studied by scanning tunneling microscopy (STM) and scanning

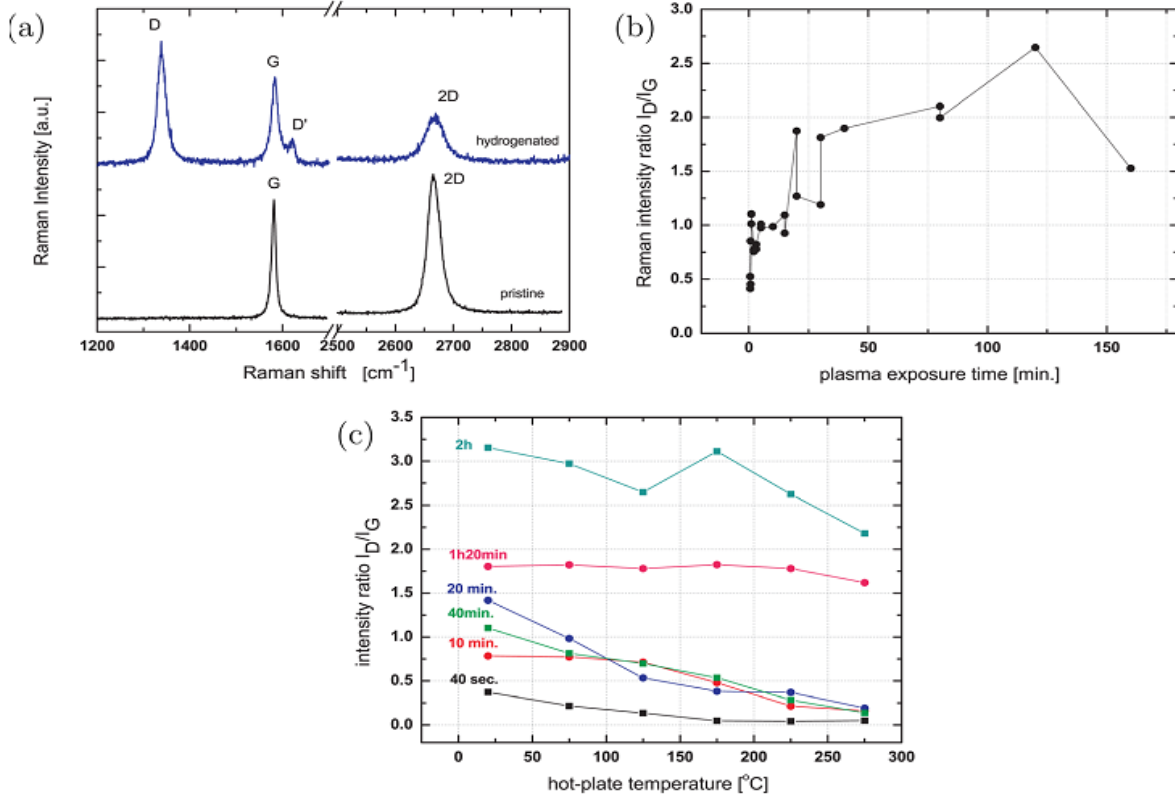


Figure 5. (a) Raman spectrum of pristine single layer graphene – SLG (black) and after 20 min of exposure to the Ar/H₂ plasma (blue) (Wojtaszek et al., 2011). Exposure induces additional Raman bands: a D band around 1340 cm⁻¹ and a weaker D' band around 1620 cm⁻¹. The increase of FWHM of original graphene bands (G, 2D) is apparent. (b) Integrated intensity ratio between the D and G bands (I_D/I_G) of SLG after different Ar/H₂ plasma exposure times. The scattering of the data for different samples is attributed to the floating potential of the graphene flake during exposure. (c) The change of the I_D/I_G ratio of exposed flakes under annealing on hot-plate for 1 min. The plasma exposure time for each flake is indicated next to the corresponding I_D/I_G values. In flakes exposed for less than 1 h the D band could be almost fully suppressed ($I_D/I_G < 0.2$), which confirms the hydrogen-type origin of defects. In longer exposed samples (80 min and 2 h), annealing does not significantly reduce I_D/I_G , which suggests a different nature of defects, e.g., vacancies.

tunneling spectroscopy (STS). The surfaces were chemically modified using 40 min Ar/H₂ plasma (with 3 W power) treatment (Figure 6) average an energy band gap of 0.4 eV around the Fermi level. Although the plasma treatment modifies the surface topography in an irreversible way, the change in the electronic properties can be reversed by moderate thermal annealing (for 10 min at 553K), and the samples can be hydrogenated again to yield a similar, but slightly reduced, semiconducting behavior after the second hydrogenation. The data (Figure 6) show that the time of desorption from both the epitaxial graphene/Ni samples and HOPG samples of about 90 to 99% of hydrogen under 553K annealing is $t_{0.9(\text{des.})553\text{K}}$ (or $t_{0.99(\text{des.})553\text{K}}$) $\approx 6 \times 10^2$ s. Hence, by using Equation (8), one can evaluate the quantity $\tau_{0.63(\text{des.})553\text{K}[52]} \approx 260$ (or 130) s, which is close (within the errors) to the similar quantity of $\tau_{0.63(\text{des.})553\text{K}[51]} \approx 70$ s for the epitaxial graphene flakes (Wojtaszek et al., 2011) (Table 2).

The data (Figure 6) also show that the time of adsorption (for both the epitaxial graphene/Ni samples and HOPG samples) of about 90 to 99% of the saturation hydrogen amount (under charging at about 300K) is $t_{0.9(\text{ads.})300\text{K}}$ (or $t_{0.99(\text{ads.})300\text{K}}$) $\approx 2.4 \times 10^3$ s. Hence, by using Equation (8)*, one can evaluate the quantity $\tau_{0.63(\text{ads.})300\text{K}[52]} \approx (1.1 \text{ or } 0.5) \times 10^2$ s, which coincides (within the errors) with the similar quantity of $\tau_{0.63(\text{ads.})300\text{K}[51]} \approx 9 \times 10^2$ s for the epitaxial graphene flakes (Wojtaszek et al., 2011) (Table 2).

The data (Figure 6) also show that the time of adsorption (for both the epitaxial graphene/Ni samples and HOPG samples) of about 90 - 99% of the saturation hydrogen amount (under charging at about 300K) is $t_{0.9(\text{ads.})300\text{K}}$ (or $t_{0.99(\text{ads.})300\text{K}}$) $\approx 2.4 \times 10^3$ s. Hence, by using Equation (8)*, one can evaluate the quantity $\tau_{0.63(\text{ads.})300\text{K}[52]} \approx (1.1 \text{ or } 0.5) \times 10^2$ s, which coincides (within the errors) with the similar quantity of $\tau_{0.63(\text{ads.})300\text{K}[51]} \approx 9 \times 10^2$ s for the epitaxial graphene

Table 2. Analytical values of some related quantities.

Material	Value/Quantity		
	$\Delta H_{(des.)}$, eV { $\Delta H_{(ads.)}$, eV}	$K_0_{(des.)}$, s ⁻¹ { $L \approx (D_{0app.III}/K_0_{(des.)})^{1/2}$ }	$\tau_{0.63(des.)553K}$, s { $\tau_{0.63(ads.)300K}$, s}
Graphene flakes/SiO ₂ (Wojtaszek et al., 2011)	0.11 ± 0.07 (as process ~ I, ~ models "F", "G", Figure 4) {0.1 ± 0.1}	0.15 (for 0.11 eV) { $L \sim d_{sample}$ }	0.7×10^2 { 0.9×10^3 }
Graphene/Ni HOPG (Castellanos-Gomez et al., 2012)			$1.3 \times 10^2 - 2.6 \times 10^2$ { $0.5 \times 10^3 - 1.0 \times 10^3$ }
SiC-D/QFMLG-H (Bocquet et al., 2012)	0.7 ± 0.2 (as processes ~ I - II, ~ model "G", Figure 4)	9×10^2 (for 0.7 eV) { $L \sim d_{sample}$ }	2.7×10^3
SiC-D/QFMLG (Bocquet et al., 2012)	2.0 ± 0.6 2.6 (as process ~ III, ~model "F*")	1×10^6 (for 2.0 eV) 6×10^8 (for 2.6 eV) { $L \approx 22$ nm}	1.7×10^{12} 8×10^{14}
Graphene/SiO ₂ (Elias et al., 2009) (Table 1A)	If 0.3 if 0.6 if 0.9 (as processes ~ I-II, ~model "G", Figure 4) {0.3 ± 0.2}	then 0.2 then 0.8×10^2 then 3.5×10^4 { $L \sim d_{sample}$ }	0.3×10^2 3.7×10^3 4.6×10^3 { 2.5×10^3 }
Graphene*/SiO ₂ (TDS-peak #3) (Elias et al., 2009) (Table 1A)	0.23 ± 0.05 (as process ~ I, ~ models "F", "G", Figure 4)	2.4(for 0.23 eV) { $L \sim d_{sample}$ }	0.5×10^2
Graphene*/SiO ₂ (TDS-peak #2) (Elias et al., 2009) (Table 1A)	0.6 ± 0.3 (as processes ~ I - II, ~ model "G", Figure 4)	1×10^6 (for 0.6 eV) { $L \sim d_{sample}$ }	0.3
Graphene*/SiO ₂ (TDS-peak #1) (Elias et al., 2009) (Table 1A)	0.6 ± 0.3 (as processes ~ I - II, ~ model "G", Figure 4)	2×10^7 (for 0.6 eV) { $L \sim d_{sample}$ }	1.5×10^{-2}

flakes (Wojtaszek et al., 2011) considered previously (Table 2).

These analytical results on characteristics of hydrogenation-dehydrogenation of epitaxial graphene and graphite surfaces (Castellanos-Gomez et al., 2012; Wojtaszek et al., 2012) (also as the results for graphene flakes (Wojtaszek et al., 2011) presented previously) may be interpreted within the models used for interpretation of the similar characteristics for the epitaxial graphenes (Elias et al., 2009) (Tables 1 and 2).

As noted in Castellanos-Gomes et al. (2012) and Arramel et al. (2012), before the plasma treatment, the CVD graphene exhibits a Moiré pattern superimposed to the honeycomb lattice of graphene (Figure 6d). This is due to the lattice parameter mismatch between the graphene and the nickel surfaces, and thus the characteristics of the most of the epitaxial graphene samples. On the other hand, as is also noted in Castellanos-Gomes et al. (2012) and Arramel et al., (2012), for the hydrogenated CVD graphene, the expected

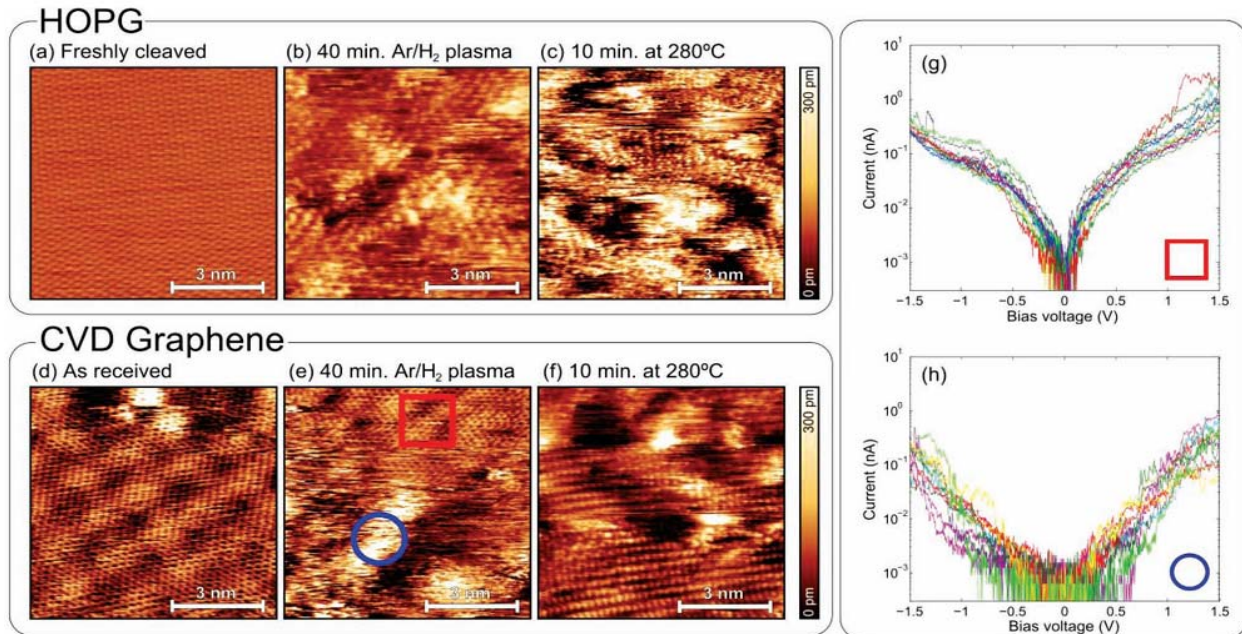


Figure 6. (a-f) Topography images acquired in the constant-current STM mode (Castellanos-Gomez, Wojtaszek et al., 2012): (a-c) HOPG, d-f) graphene grown by CVD on top of a nickel surface at different steps of the hydrogenation/dehydrogenation process. a,d) Topography of the surface before the hydrogen plasma treatment. For the HOPG, the typical triangular lattice can be resolved all over the surface. For the CVD graphene, a Moiré pattern, due to the lattice mismatch between the graphene and the nickel lattices, superimposed onto the honeycomb lattice is observed. b,e) After 40 min of Ar/H₂ plasma treatment, the roughness of the surfaces increases. The surfaces are covered with bright spots where the atomic resolution is lost or strongly distorted. c,f) graphene surface after 10 min of moderate annealing; the topography of both the HOPG and CVD graphene surfaces does not fully recover its original crystallinity. g) Current-voltage traces measured for a CVD graphene sample in several regions with pristine atomic resolution, such as the one marked with the red square in (e). h) The same as (g) but measured in several bright regions, such as the one marked with the blue circle in (e), where the atomic resolution is distorted.

structural changes are twofold. First, the chemisorption of hydrogen atoms will change the sp^2 hybridization of carbon atoms to tetragonal sp^3 hybridization, modifying the surface geometry. Second, the impact of heavy Ar ions, present in the plasma, could also modify the surface by inducing geometrical displacement of carbon atoms (rippling graphene surface) or creating vacancies and other defects (for instance, grain or domain boundaries (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011; Koepke et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012)). Figure 6e shows the topography image of the surface CVD graphene after the extended (40 min) plasma treatment. The nano-order-corrugation increases after the treatment, and there are brighter nano-regions (of about 1 nm in height and several nm in diameter) in which the atomic resolution is lost or strongly distorted. It was also found (Castellanos-Gomez, Wojtaszek et al., 2012; Castellanos-Gomez, Arramel et al., 2012) that these bright nano-regions present a semiconducting behavior, while the rest of the surface remains conducting (Figure 6g to h).

It is reasonable to assume that most of the chemisorbed hydrogen is localized into these bright nano-regions, which have a blister-like form. Moreover, it is also reasonable to assume that the monolayer (single) graphene flakes on the Ni substrate are permeable to atomic hydrogen only in these defected nano-regions. This problem has been formulated in Introduction. A similar model may be valid and relevant for the HOPG samples (Figure 6a to c).

It has been found out that when graphene is deposited on a SiO₂ surface (Figures 7 and 8) the charged impurities presented in the graphene/substrate interface produce strong inhomogeneities of the electronic properties of graphene. On the other hand, it has also been shown how homogeneous graphene grown by CVD can be altered by chemical modification of its surface by the chemisorption of hydrogen. It strongly depresses the local conductance at low biases, indicating the opening of a band gap in graphene (Castellanos-Gomez, Arramel et al., 2012; Castellanos-Gomez, Smit et al., 2012).

The charge inhomogeneities (defects) of epitaxial hydrogenated graphene/SiO₂ samples do not show long range ordering, and the mean spacing between them is

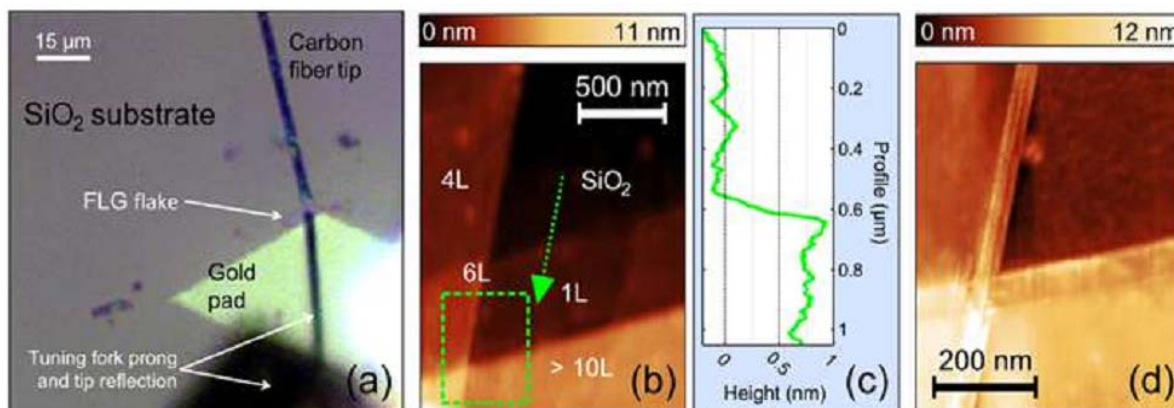


Figure 7. (a) Optical image of the coarse tip positioning on a few-layers graphene flake on the SiO₂ substrate, (b) AFM topography image of the interface between the few-layers graphene flake and the the SiO₂ substrate and areas with different number of layers (labeled as >10, 6, 4 and 1 L) are found, (c) Topographic line profile acquired along the dotted line in (b), showing the interface between the SiO₂ substrate and a monolayer (1L) graphene region, and (d) STM topography image of the regions marked by the dashed rectangle in (b) (Castellanos-Gomez, 2012; Arramel et al., 2012; Castellanos-Gomez, 2012; Smit et al., 2012).

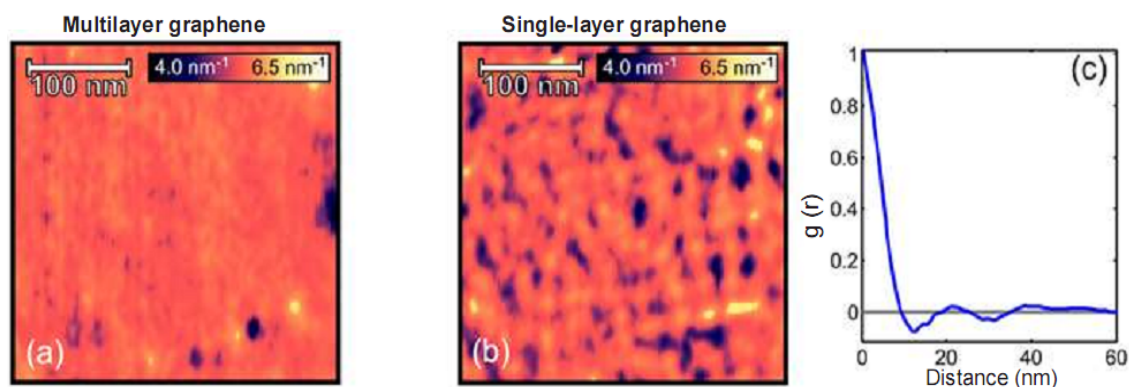


Figure 8. (a) and (b) show the local tunneling decay constant maps measured on a multilayer and a single-layer (1 L) region, respectively. (c) Radial autocorrelation function of the local tunneling decay image in (b) (Castellanos-Gomez, 2012; Arramel et al., 2012; Castellanos-Gomez, 2012; Smit et al., 2012).

$L_{\text{def.}} \approx 20$ nm (Figure 8). It is reasonable to assume that the charge inhomogeneities (defects) are located at the interface between the SiO₂ layer (300 nm thick) and the graphene flake (Castellanos-Gomez, 2012; Arramel et al., 2012; Smit et al., 2012). A similar quantity [$L_{\text{def.}} \approx 11 - 17$ nm, (Wojtaszek et al., 2011)] for the hydrogen adsorption centers in the monolayer graphene flakes on the SiO₂ substrate has been above considered.

In Bocquet et al. (2012), hydrogenation of deuterium-intercalated quasi-free-standing monolayer graphene on SiC(0001) was obtained and studied with LEED and HREELS. While the carbon honeycomb structure remained intact, it has shown a significant band gap opening in the hydrogenated material. Vibrational spectroscopy evidences for hydrogen chemisorption on the quasi-free-standing

graphene has been provided and its thermal stability has been studied (Figure 9). Deuterium intercalation, transforming the buffer layer in quasi-free-standing monolayer graphene (denoted as SiC-D/QFMLG), has been performed with a D atom exposure of $\sim 5 \times 10^{17}$ cm⁻² at a surface temperature of 950K. Finally, hydrogenation up to saturation of quasi-free-standing monolayer graphene has been performed at room temperature with H atom exposure $> 3 \times 10^{15}$ cm⁻². The latter sample has been denoted as SiC-D/QFMLG-H to stress the different isotopes used.

According to a private communication from R. Bisson, the temperature indicated at each point in Figure 9 corresponds to successive temperature ramp (not linear) of 5 min. Within a formal kinetics approach for the first order reactions (Nechaev, 2010; Bazarov, 1976), one can

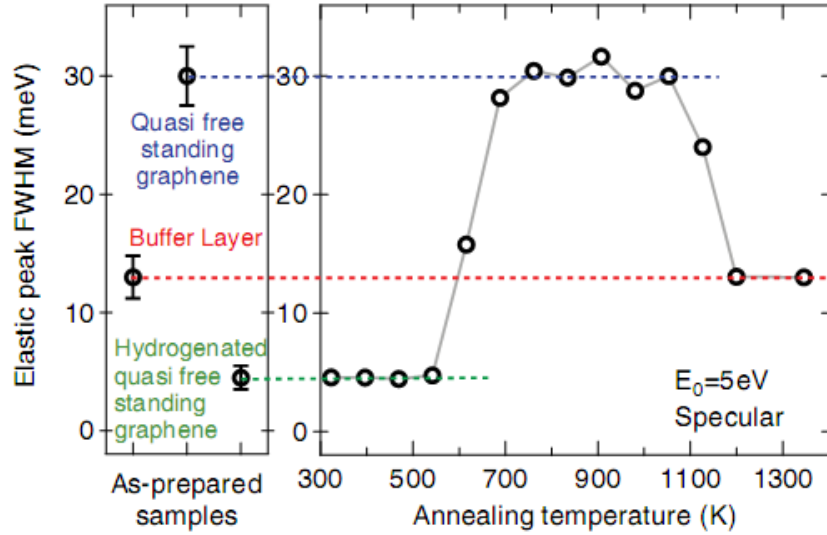


Figure 9. Evaluation of the HREELS elastic peak FWHM of SiC-D/QFMLG-H upon annealing. The uncertain annealing temperature is estimated to be $\pm 5\%$. Error bars represent the $\pm\sigma$ variation of FWHM measured across the entire surface of several samples (Bocquet et al., 2012).

treat the above noted points at $T_i = 543, 611$ and 686 K, by using Equation (8) transformed to a more suitable form (8'): $K_i \approx -(\ln(C/C_{0i})/t)$, where $t = 300$ s, and the corresponding quantities C_{0i} and C are determined from Figure 9. It resulted in finding values of the reaction (hydrogen desorption from SiC-D/QFMLG-H samples) rate constant $K_{i(\text{des.})}$ for 3 temperatures: $T_i = 543, 611$ and 686 K. The temperature dependence is described by Equation (9). Hence, the desired quantities have been determined (Table 2) as the reaction (hydrogen desorption) activation energy $\Delta H_{(\text{des.})(\text{SiC-D/QFMLG-H})[55]} = 0.7 \pm 0.2$ eV, and the per-exponential factor of the reaction rate constant $K_{0(\text{des.})(\text{SiC-D/QFMLG-H})[55]} \approx 9 \times 10^2$ s⁻¹. The obtained value of $\Delta H_{(\text{des.})(\text{SiC-D/QFMLG-H})[55]}$ is close (within the errors) to the similar ones ($E_{\text{TDS-peak \#1}[5]}$ and $E_{\text{TDS-peak \#2}[5]}$) for TDS processes #1 and #2 (Table 1A). But the obtained value $K_{0(\text{des.})(\text{SiC-D/QFMLG-H})[55]}$ differs by several orders from the similar ones ($K_{0(\text{des.})(\text{TDS-peak \#1})[5]}$ and $K_{0(\text{des.})(\text{TDS-peak \#2})[5]}$) for TDS processes #1 and #2 (Table 1A). Nevertheless, these three desorption processes may be related to chemisorption models “H” and/or “G” (Figure 4).

These analytical results on characteristics of hydrogen desorption (dehydrogenation) from (of) SiC-D/QFMLG-H samples (Bocquet et al., 2012) may be also (as the previous results) interpreted within the models used for interpretation of the similar characteristics for the epitaxial graphenes (Elias et al., 2009) (Tables 1A and 2).

In the same way, one can treat the points from Figure 9 (at $T_i = 1010, 1120$ and 1200 K), which are related to the intercalated deuterium desorption from SiC-D/QFMLG samples. This results in finding the desired quantities

(Table 2): the reaction (deuterium desorption) activation energy $\Delta H_{(\text{des.})(\text{SiC-D/QFMLG})[55]} = 2.0 \pm 0.6$ eV, and the per-exponential factor of the reaction rate constant $K_{0(\text{des.})(\text{SiC-D/QFMLG})[55]} \approx 1 \times 10^6$ s⁻¹.

Such a relatively low (in comparison with the vibration C-H or C-D frequencies) value of $K_{0(\text{des.})(\text{SiC-D/QFMLG})[55]}$, points out that the process cannot be described within the Polanyi-Wigner model (Nechaev, 2010; Nechaev and Veziroglu, 2013), related to the case of a non-diffusion rate limiting kinetics.

And as concluded in Bocquet et al. (2012), the exact intercalation mechanism of hydrogen diffusion through the anchored graphene lattice, at a defect or at a boundary of the anchored graphene layer, remains an open question.

Formally, this desorption process (obviously, of a diffusion-limiting character) may be described (as shown below) similarly to TDS process III (model “F*”) (Table 1B), and the apparent diffusion activation energy may be close to the break-down energies of the C-H bonds.

Obviously such analytical results on characteristics of deuterium desorption from SiC-D/QFMLG samples (Bocquet et al., 2012) may not be interpreted within the models used for interpretation of the similar characteristics for the epitaxial graphenes (Elias et al., 2009) (Tables 1A and 2).

But these results (for SiC-D/QFMLG samples of Bocquet et al. (2012) may be quantitatively interpreted on the basis of using the characteristics of process III (Table 1B). Indeed, by using the quantities' values (from Table 1) of $\Delta H_{(\text{des.})(\text{SiC-D/QFMLG})[55]} \approx Q_{\text{app.III}} \approx 2.6$ eV, $K_{0(\text{des.})(\text{SiC-D/QFMLG})[55]} \approx 6 \times 10^8$ s⁻¹ and $D_{0\text{app.III}} \approx 3 \times 10^{-3}$ cm²/s, one

can evaluate the quantity of $L \approx (D_{0app,III} / K_{0(des.)})^{1/2} = 22$ nm. The obtained value of L coincides (within the errors) with values of the quantities of $L_{def.} \approx 11 - 17$ nm [Equation (10)] and $L_{def.} \approx 20$ nm (Figure 8b). It shows that in the case under consideration, the intercalation mechanism of hydrogen (deuterium) diffusion through the anchored graphene lattice at the corresponding point type defects (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011; Koepke et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012), of the anchored graphene layer may have place. And the desorption process of the intercalated deuterium may be rate-limited by diffusion of deuterium atoms to a nearest one of such point type defects of the anchored graphene layer.

It is reasonable to assume that the quasi-free-standing monolayer graphene on the SiC-D substrate is permeable to atomic hydrogen (at room temperature) in some defect nano-regions (probably, in vacancies and/or triple junctions (nodes) of the grain-boundary network (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011; Koepke et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012).

It would be expedient to note that the HREELS data (Bocquet et al., 2012) on bending and stretching vibration C-H frequencies in SiC-D/QFMLG-H samples [153 meV ($3.7 \times 10^{13} \text{ s}^{-1}$) and 331 meV ($8.0 \times 10^{13} \text{ s}^{-1}$), respectively] are consistent with those (Xie et al., 2011) considered above, related to the HREELS data for the epitaxial graphene (Elias et al., 2009).

The obtained characteristics (Table 2) of desorption processes (Wojtaszek et al., 2011; Castellanos-Gomez, 2012; Wojtaszek et al., 2012; Bocquet et al., 2012) show that all these processes may be of a diffusion-rate-controlling character (Nechaev, 2010).

CONSIDERATION AND INTERPRETATION OF THE RAMAN SPECTROSCOPY DATA ON DEHYDROGENATION OF GRAPHENE LAYERS ON SiO₂ SUBSTRATE

In Luo et al. (2009), graphene layers on SiO₂/Si substrate have been chemically decorated by radio frequency hydrogen plasma (the power of 5 - 15 W, the pressure of 1 T or) treatment for 1 min. The investigation of hydrogen coverage by Raman spectroscopy and micro-x-ray photoelectron spectroscopy (PES) characterization demonstrates that the hydrogenation of a single layer graphene on SiO₂/Si substrate is much less feasible than that of bi-layer and multilayer graphene. Both the hydrogenation and dehydrogenation processes of the graphene layers are controlled by the corresponding energy barriers, which show significant dependence on the number of layers. These results (Luo et al., 2009) on

bilayer graphene/SiO₂/Si are in contradiction to the results (Elias et al., 2009) on a negligible hydrogenation of bi-layer epitaxial graphene on SiO₂/Si wafer, when obviously other defects are produced.

Within a formal kinetics approach (Nechaev, 2010; Bazarov, 1976), the kinetic data from (Figure 10a) for single layer graphene samples (1LG-5W and 1LG-15W ones) can be treated. Equation (7) is used to transform into a more suitable form (7'): $K \approx -[(\Delta C/\Delta t)/C]$, where $\Delta t = 1800$ s, and ΔC and C are determined from Figure 10a. The results have been obtained for 1LG-15W sample 3 values of the #1 reaction rate constant $K_{1(1LG-15W)}$ for 3 temperatures ($T = 373, 398$ and 423 K), and 3 values of the #2 reaction rate constant $K_{2(1LG-15W)}$ for 3 temperatures ($T = 523, 573$ and 623 K). Hence, by using Equation 9, the following quantities for 1LG-15W samples have been determined (Table 3): the #1 reaction activation energy $\Delta H_{des.1(1LG-15W)} = 0.6 \pm 0.2$ eV, the per-exponential factor of the #1 reaction rate constant $K_{0des.1(1LG-15W)} \approx 2 \times 10^4 \text{ s}^{-1}$, the #2 reaction activation energy $\Delta H_{des.2(1LG-15W)} = 0.19 \pm 0.07$ eV, and the per-exponential factor of the #2 reaction rate constant $K_{0des.2(1LG-15W)} \approx 3 \times 10^{-2} \text{ s}^{-1}$.

This also resulted in finding for 1LG-5W sample 4 values of the #1 reaction rate constant $K_{1(1LG-5W)}$ for 4 temperatures ($T = 348, 373, 398$ and 423 K), and 2 values of the #2 reaction rate constant $K_{2(1LG-5W)}$ for 2 temperatures ($T = 523$ and 573 K). Therefore, by using Equation 9, one can evaluate the desired quantities for 1LG-5W specimens (Table 3): the #1 reaction activation energy $\Delta H_{des.1(1LG-5W)} = 0.15 \pm 0.04$ eV, the per-exponential factor of the #1 reaction rate constant $K_{0des.1(1LG-5W)} \approx 2 \times 10^{-2} \text{ s}^{-1}$, the #2 reaction activation energy $\Delta H_{des.2(1LG-5W)} = 0.31 \pm 0.07$ eV, and the per-exponential factor of the #2 reaction rate constant $K_{0des.2(1LG-5W)} \approx 0.5 \text{ s}^{-1}$.

A similar treatment of the kinetic data from (Figure 10c) for bi-layer graphene 2LG-15W samples resulted in obtaining 4 values of the #2 reaction rate constant $K_{2(2LG-15W)}$ for 4 temperatures ($T = 623, 673, 723$ and 773 K). Hence, by using Equation (9), the following desired values are found (Table 3): the #2 reaction activation energy $\Delta H_{des.2(2LG-15W)} = 0.9 \pm 0.3$ eV, the per-exponential factor of the #2 reaction rate constant $K_{0des.2(2LG-15W)} \approx 1 \times 10^3 \text{ s}^{-1}$.

A similar treatment of the kinetic data from (Figure 6c) in Luo et al. (2009) for bi-layer graphene 2LG-5W samples results in obtaining 4 values for the #1 reaction rate constant $K_{1(2LG-5W)}$ for 4 temperatures ($T = 348, 373, 398$ and 423 K), and 3 values for the #2 reaction rate constant $K_{2(2LG-5W)}$ for 3 temperatures ($T = 573, 623$ and 673 K). Their temperature dependence is described by Equation (9). Hence, one can evaluate the following desired values (Table 3): the #1 reaction activation energy $\Delta H_{des.1(2LG-5W)} = 0.50 \pm 0.15$ eV, the per-exponential factor of the #1 reaction rate constant $K_{0des.1(2LG-5W)} \approx 2 \cdot 10^3 \text{ s}^{-1}$, the #2 reaction activation energy $\Delta H_{des.2(2LG-5W)} = 0.40 \pm 0.15$ eV, and the per-exponential

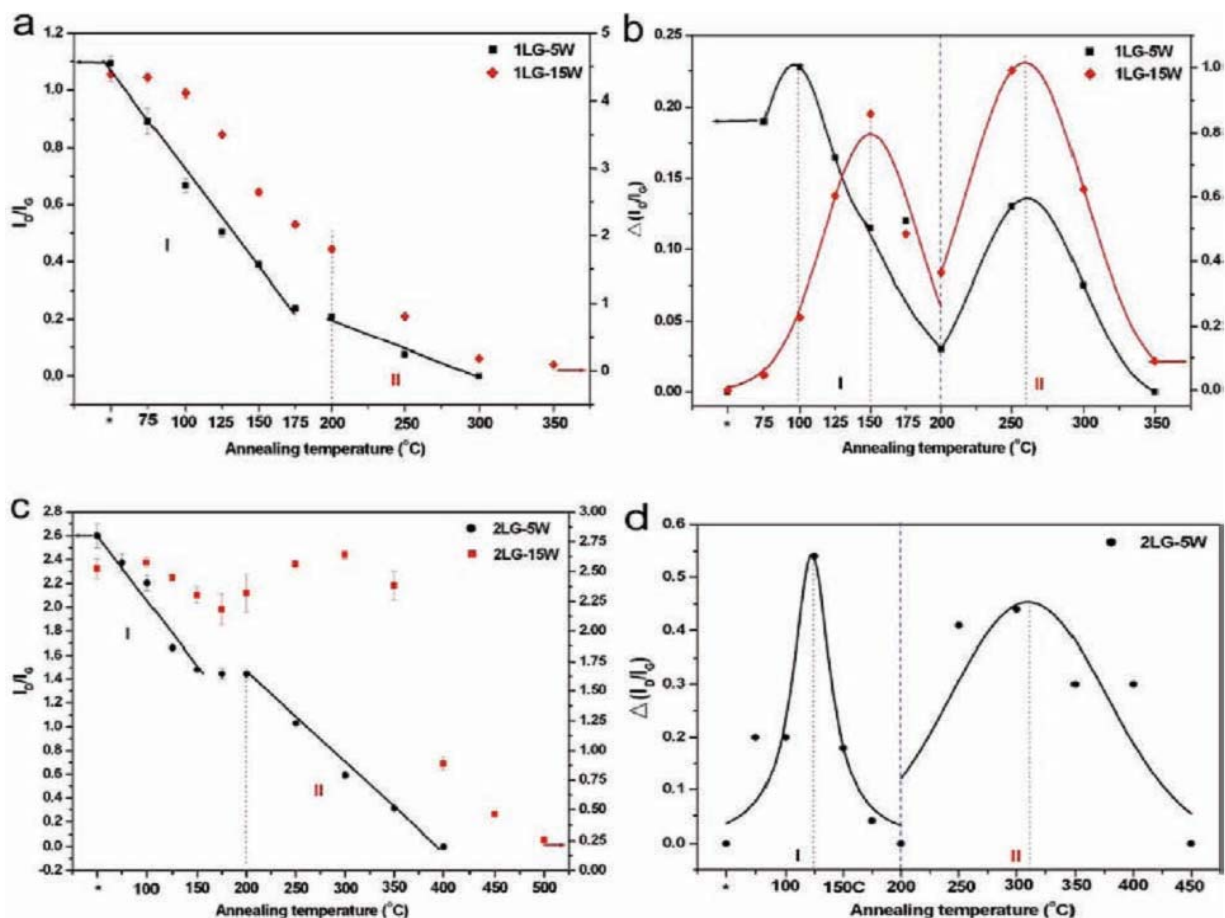


Figure 10. (a) The evolution of the D and G band intensity ratio (I_D/I_G) with annealing temperatures of 1LG (single-layer graphene) hydrogenated by 5 and 15 W (the power), 1 Torr hydrogen plasma for 1 min (Luo et al. (2009)); (b) the evolution of $\Delta(I_D/I_G)$ with annealing temperatures of 1 LG hydrogenated by 5 and 15 W, 1 Torr hydrogen plasma for 1 min; (c) the evolution of the D and G band intensity ratio (I_D/I_G) with annealing temperatures of 2LG (bi-layer graphene) hydrogenated by 5 and 15 W, 1 Torr hydrogen plasma for 1 min; (d) the evolution of $\Delta(I_D/I_G)$ with annealing temperatures of 2LG hydrogenated by 5 and 15 W, 1 Torr hydrogen plasma for 1 min. The asterisk (*) denotes the as-treated sample by H_2 plasma.

factor of the #2 reaction rate constant $K_{0des,2(2LG-5W)} \approx 1 \text{ s}^{-1}$.

The obtained analytical results (Table 3) on characteristics of desorption (dehydrogenation) processes #1 and #2 (Luo et al., 2009) may be interpreted within the models used for interpretation of the similar characteristics for the epitaxial graphenes (Elias et al., 2009) (Table 1A). It shows that the desorption processes #1 and #2 in Luo et al. (2009) may be of a diffusion-rate-controlling character.

CONSIDERATION AND INTERPRETATION OF THE TDS/STM DATA FOR HOPG TREATED BY ATOMIC DEUTERIUM

Hornekaer et al. (2006) present results of a STM study of HOPG samples treated by atomic deuterium, which

reveals the existence of two distinct hydrogen dimer nano-states on graphite basal planes (Figures 11 and 12b). The density functional theory calculations allow them to identify the atomic structure of these nano-states and to determine their recombination and desorption pathways. As predicted, the direct recombination is only possible from one of the two dimer nano-states. In conclusion (Hornekaer et al., 2006), this results in an increased stability of one dimer nanospecies, and explains the puzzling double peak structure observed in temperature programmed desorption spectra (TPD or TDS) for hydrogen on graphite (Figure 12a).

By using the method of Nechaev (2010) of TDS peaks' treatment, for the case of TDS peak 1 (~65% of the total area, $T_{max\#1} \approx 473\text{K}$) in Figure 12), one can obtain values of the reaction #1 rate constant ($K_{(des.)1} = 1/\tau_{0.63(des.)1}$) for several temperatures (for instance, $T = 458, 482$ and 496K). Their temperature dependence can be described

Table 3. Analytical values of some related quantities.

Sample	Values/Quantities			
	$\Delta H_{(des.)1}$ (eV)	$K_{0(des.)1}$ (s^{-1}) {L}	$\Delta H_{(des.)2}$ (eV)	$K_{0(des.)2}$ (s^{-1}) {L}
1LG-15W (graphene) (Luo et al., 2009)	0.6 ± 0.2 (as processes ~I-II, ~model "G", Figure 4)	2×10^4 {L ~ d_{sample} }	0.19 ± 0.07 (as process~I, ~models "F", "G", Figure 4)	3×10^{-2} {L ~ d_{sample} }
2LG-15W (bi-graphene) (Luo et al., 2009)			0.9 ± 0.3 (as processes~I-II, ~model"G",Figure 4)	1×10^3 {L ~ d_{sample} }
1LG-5W (graphene) (Luo et al., 2009)	0.15 ± 0.04 (as process~ I, ~ models "F", "G",Figure 4)	2×10^{-2} {L ~ d_{sample} }	0.31 ± 0.07 (as process ~ I [14], ~models "F" , "G", Figure 4)	5×10^{-1} {L ~ d_{sample} }
2LG-5W (bi-graphene) (Luo et al., 2009)	0.50 ± 0.15 (as processes ~I-II, ~model"G", Figure 4)	2×10^3 {L ~ d_{sample} }	0.40 ± 0.15 (as processes ~ I-II, ~model "G", Figure 4)	1.0 {L ~ d_{sample} }
HOPG (Hornekaer et al., 2006), TDS-peaks 1, 2	0.6 ± 0.2 (as processes ~ I - II, ~model"G", Figure 4)	1.5×10^4 {L ~ d_{sample} }	1.0 ± 0.3 (as processes ~ I-II, ~ model "G", Figure 4)	2×10^6 {L ~ d_{sample} }
Graphene/SiC (Watcharinyanon et al., 2011)			3.6 (as process ~IV [14],~models "C", "D",Figure 4)	2×10^{14} ~ $V_{(C-H)}$ {L~ 17nm}
HOPG, TDS-peaks 1, 2 HOPG, TDS-peak 1 (Waqar et al., 2000)	2.4 (Waqar et al., 2000) (as process~III,~model "F*") 2.4 ± 0.5 (as process ~ III,~model "F*")	2×10^{10} {L~4 nm}	4.1 (Waqar et al., 2000) (as process~IV, ~models "C", "D", Figure 4)	

by Equation (9). Hence, the desired values are defined as follows (Table 3): the #1 reaction (desorption) activation energy $\Delta H_{(des.)1} = 0.6 \pm 0.2$ eV, and the per-exponential factor of the #1 reaction rate constant $K_{0(des.)1} \approx 1.5 \times 10^4 s^{-1}$.

In a similar way, for the case of TDS peak 2 (~35% of the total area, $T_{max\#2} \approx 588$ K) in Figure 12a, one can obtain values of the #2 reaction rate constant ($K_{(des.)2} = 1/\tau_{0.63(des.)2}$) for several temperatures (for instance, $T = 561$ and 607 K). Hence, the desired values are defined as follows (Table 3): the #2 reaction (desorption) activation energy $\Delta H_{(des.)2} = 1.0 \pm 0.3$ eV, and the per-exponential factor of the #2 reaction rate constant $K_{0(des.)2} \approx 2 \times 10^6 s^{-1}$. The obtained analytical results (Table 3) on characteristics of desorption (dehydrogenation) processes #1 and #2 in Hornekaer et al. (2006) (also as in Luo et al. (2009) may be interpreted within the models used above for interpretation of the similar characteristics for the epitaxial graphenes (Elias et al., 2009) (Table 1A).

It shows that the desorption processes #1 and #2 (in Hornekaer et al. (2006) and Luo et al. (2009) may be of a diffusion-rate-controlling character. Therefore, these processes cannot be described by using the Polanyi-Wigner equation (as it has been done in Hornekaer et al. (2006).

The observed "dimer nano-states" or "nano-protrusions" (Figures 11 and 12b) may be related to the defected nano-regions, probably, as grain (domain) boundaries (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011; Koepke et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012), and/or triple and other junctions (nodes) of the grain-boundary network in the HOPG samples. Some defected nano-regions at the grain boundary network (hydrogen adsorption centres #1, mainly, the "dimer B" nano-structures) can be related to TPD (TDS) peak 1, the others (hydrogen adsorption

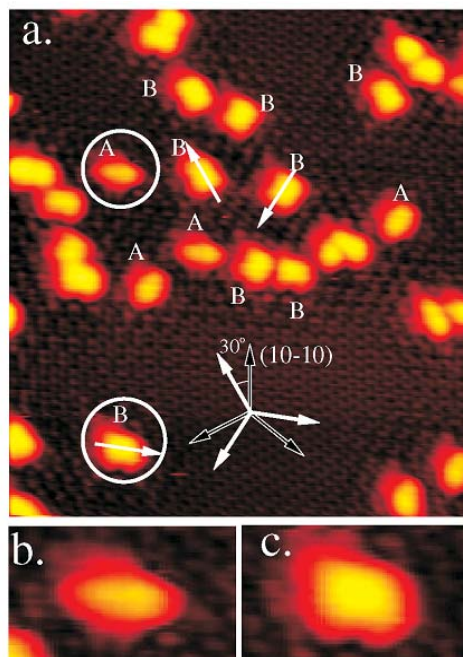


Figure 11. (a) STM image ($103 \times 114 \text{ \AA}^2$) of dimer structures of hydrogen atoms on the graphite surface after a 1 min deposition at room temperature (Hornekaer et al., 2006). Imaging parameters: $V_t = 884 \text{ mV}$, $I_t = 160 \text{ pA}$. Examples of dimer type A and B are marked. Black arrows indicate $\langle 21\bar{1}0 \rangle$ directions and white arrows indicate the orientation of the dimers 30° off. (c) Close up of dimer B structure in lower white circle in image (a).

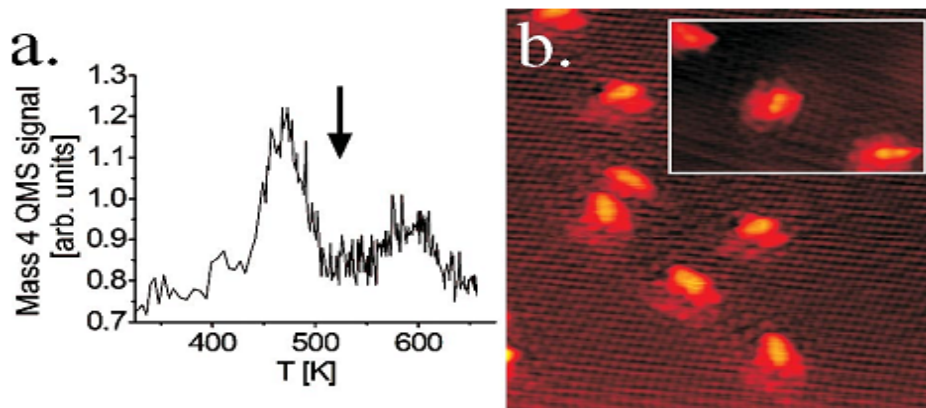


Figure 12. (a) A mass 4 amu, i.e., D_2 , TPD spectrum from the HOPG surface after a 2 min D atom dose (ramp rate: 2 K/s below 450 K , 1 K/s above) (Hornekaer et al., 2006). The arrow indicates the maximum temperature of the thermal anneal performed before recording the STM image in (b). (b) STM image ($103 \times 114 \text{ \AA}^2$) of dimer structures of hydrogen atoms on the graphite surface after a 1 min deposition at room temperature and subsequent anneal to 525 K (ramp rate: 1 K/s , 30 s dwell at maximum temperature). Imaging parameters: $V_t = 884 \text{ mV}$, $I_t = 190 \text{ pA}$. The inset shows a higher resolution STM image of dimer structures of hydrogen atoms on the graphite surface after a 6 min deposition at room temperature and subsequent anneal to 550 K . Imaging parameters: $V_t = -884 \text{ mV}$, $I_t = -210 \text{ pA}$.

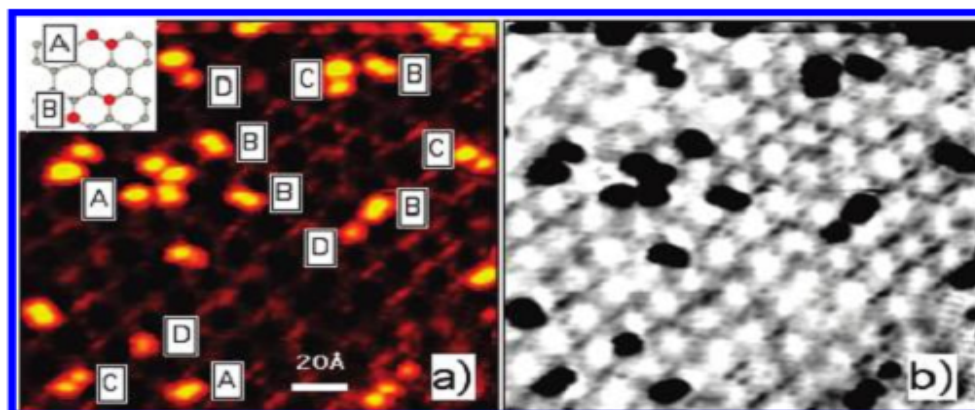


Figure 13. (a) Scanning tunneling microscopy (STM) image of hydrogenated graphene (Balog et al., 2009). The bright protrusions visible in the image are atomic hydrogen adsorbate structures identified as A = ortho-dimers, B = para-dimers, C = elongated dimers, D = monomers (imaging parameters: $V_t = -0.245$ V, $I_t = -0.26$ nA). Inset in (a); Schematic of the A ortho- and B para-dimer configuration on the graphene lattice. (b) Same image as in (a) with inverted color scheme, giving emphasis to preferential hydrogen adsorption along the 6×6 modulation on the SiC (0001)-(1 \times 10 surface). Hydrogen dose at $T_{\text{beam}} = 1600$ K, $t = 5$ s, $F = 10^{12}$ - 10^{13} atoms/cm² s.

centres #2, mainly, the “dimer A” nano-structures) to TPD (TDS) peak 2. In Figures 11a and 12b, one can imagine some grain boundary network (with the grain size of about 2 - 5 nm) decorated (obviously, in some nano-regions at grain boundaries) by some bright nano-protrusions. Similar “nano-protrusions” are observed and in graphene/SiC systems (Balog et al., 2009; Watcharinyanon et al., 2011) (Figures 13 to 16).

In Balog et al. (2009), hydrogenation was studied by a beam of atomic deuterium $10^{12} - 10^{13}$ cm⁻²s⁻¹ (corresponding to $P_D \approx 10^{-4}$ Pa) at 1600K, and the time of exposure of 5 - 90 s, for single graphene on SiC-substrate. The formation of graphene blisters were observed, and intercalated with hydrogen in them (Figures 13 and 14), similar to those observed on graphite (Hornekaer et al., 2006) (Figures 11 and 12) and graphene/SiO₂ (Watcharinyanon et al., 2011) (Figures 15 and 16). The blisters (Balog et al., 2009) disappeared after keeping the samples in vacuum at 1073K (~ 15 min). By using Equation (8), one can evaluate the quantity of $\tau_{0.63(\text{des.})1073K[58]} \approx 5$ min, which coincides (within the errors) with the similar quantity of $\tau_{0.63(\text{des.})1073K[17]} \approx 7$ min evaluated for graphene/SiC samples (Watcharinyanon et al., 2011) (Table 3).

A nearly complete decoration of the grain boundary network (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011; Koepke et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012), can be imagined in Figure 15b. Also, as seen in Figure 16, such decoration of the nano-regions obviously, located at the grain boundaries (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011; Koepke

et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012), has a blister-like cross-section height of about 1.7 nm and width of 10 nm order.

According to the thermodynamic analysis presented above, Equation (15), such blister-like decoration nano-regions (obviously, located at the grain boundaries (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011; Koepke et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012), may contain the intercalated gaseous molecular hydrogen at a high pressure.

CONSIDERATION AND INTERPRETATION OF THE PES/ARPES DATA ON HYDROGENATION-DEHYDROGENATION OF GRAPHENE/SiC SAMPLES

In Watcharinyanon et al. (2011), atomic hydrogen exposures at a pressure of $P_H \approx 1 \times 10^{-4}$ Pa and temperature $T = 973$ K on a monolayer graphene grown on the SiC(0001) surface are shown, to result in hydrogen intercalation. The hydrogen intercalation induces a transformation of the monolayer graphene and the carbon buffer layer to bi-layer graphene without a buffer layer. The STM, LEED, and core-level PES measurements reveal that hydrogen atoms can go underneath the graphene and the carbon buffer layer. This transforms the buffer layer into a second graphene layer. Hydrogen exposure (15 min) results initially in the formation of bi-layer graphene (blister-like) islands with a height of ~ 0.17 nm and a linear size of ~ 20 - 40 nm, covering about 40% of the sample (Figures 15b and e),

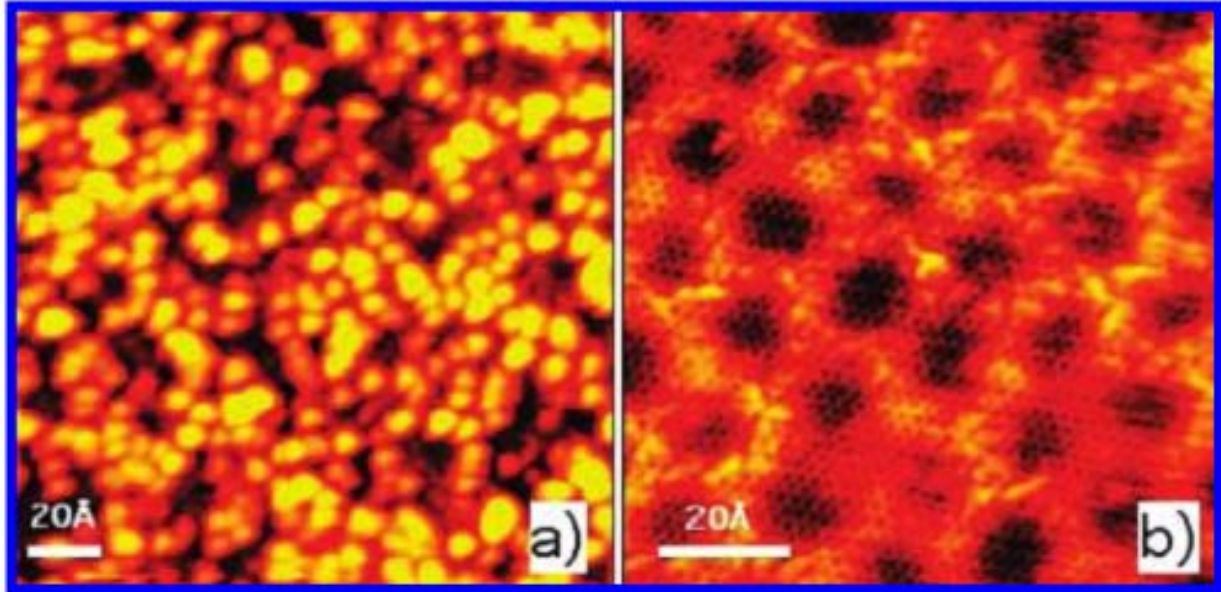


Figure 14. (a) STM image of the graphene surface after extended hydrogen exposure (Balog et al., 2009). The bright protrusions visible in the image are atomic hydrogen clusters (imaging parameters: $V_t = -0.36$ V, $I_t = -0.32$ nA). Hydrogen dose at $T = 1600$ K, $t = 90$ s, $F = 10^{12}\text{-}10^{13}$ atoms/cm² s. (b) Large graphene area recovered from hydrogenation by annealing to 1073 K (imaging parameters: $V_t = -0.38$ V, $I_t = -0.41$ nA).

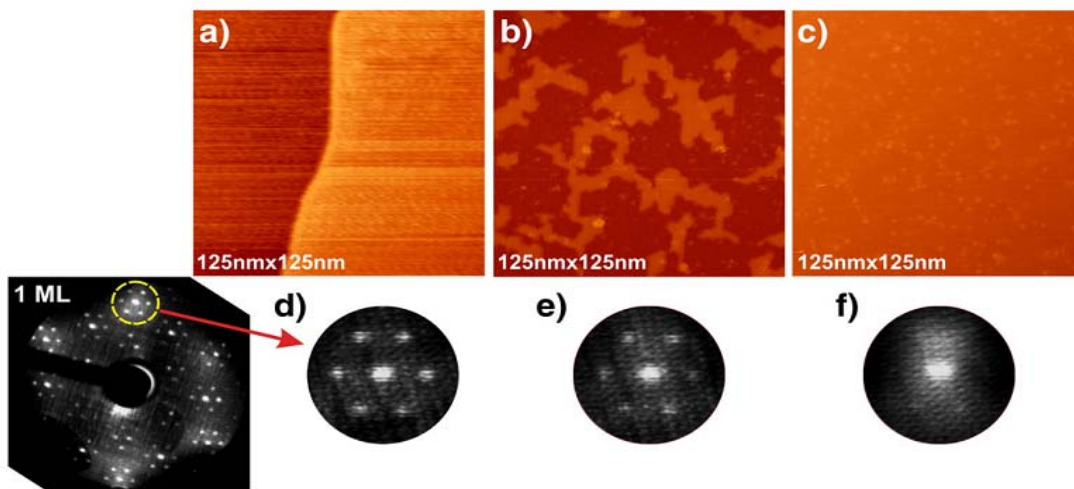


Figure 15. STM images (Watcharinyanon et al., 2011) collected at $V = -1$ V and $I = 500$ pA of a) monolayer graphene, b) after a small hydrogen exposure, and c) after a large hydrogen exposure. d) Selected part of the LEED pattern collected at $E = 107$ eV from monolayer graphene, e) after a small hydrogen exposure, and f) after a large hydrogen exposure.

16a and b). With larger (additional 15 min) atomic hydrogen exposures, the islands grow in size and merge until the surface is fully covered with bi-layer grapheme (Figures 15c and 15f, 16c and d). A $(\sqrt{3} \times \sqrt{3}) R30^\circ$ periodicity is observed on the bi-layer areas. Angle resolved PES and energy filtered X-ray photoelectron emission microscopy (XPEEM) investigations of the

electron band structure confirm that after hydrogenation the single π -band characteristic of monolayer graphene is replaced by two π -bands that represent bi-layer graphene. Annealing an intercalated sample, representing bi-layer graphene, to a temperature of 1123K or higher, re-establishes the monolayer graphene with a buffer layer on SiC (0001).

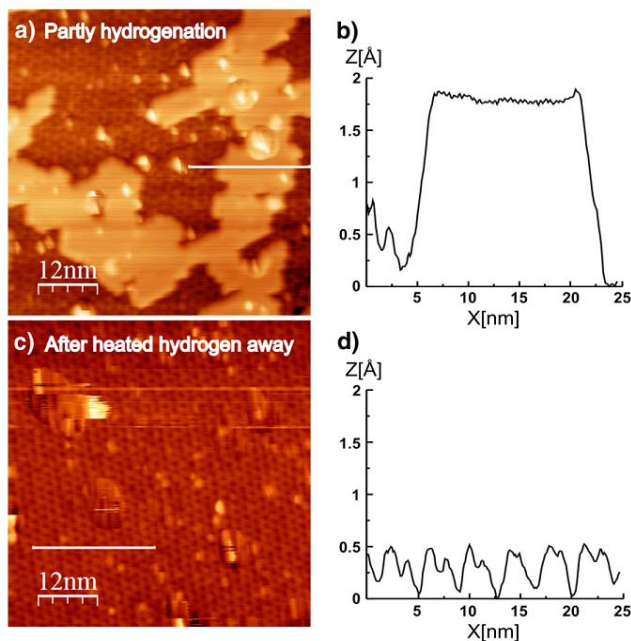


Figure 16. STM images (Watcharinyanon et al., 2011) of a) an island created by the hydrogen exposure ($V = -1$ V, $I = 500$ pA), b) line profile across the island, c) a dehydrogenated sample showing mainly $(6\sqrt{3} \times 6\sqrt{3})R30^\circ$ structure from the buffer layer ($V = -2$ V, $I = 100$ pA), and d) line profile across the $(6\sqrt{3} \times 6\sqrt{3})R30^\circ$ structure.

The dehydrogenation has been performed by subsequently annealing (for a few minutes) the hydrogenated samples at different temperatures, from 1023 to 1273K. After each annealing step, the depletion of hydrogen has been probed by PES and ARPES (Figures 17 and 18). From this data, using Equations (8) and (9), one can determine the following tentative quantities: $\tau_{0.63(\text{des.})}$ (at 1023 and 1123K), $\Delta H_{(\text{des.})} \approx 3.6$ eV and $K_{0(\text{des.})} \approx 2 \times 10^{14} \text{ s}^{-1}$ (Table 3).

The obtained value of the quantity of $\Delta H_{(\text{des.})}$ coincides (within the errors) with values of the quantities of $Q_{\text{app.IV}} \approx 3.8$ eV $\approx \Delta H_{(\text{C-H})\text{C}^{\text{C}},\text{D}}$ (Table 1B), which are related to the diffusion-rate-limiting TDS process IV of a dissociative chemisorption of molecular hydrogen in defected regions in graphite materials (Table 1B), and to the chemisorption models “C” and “D”(Figure 4).

The obtained value of the quantity of $K_{0(\text{des.})}$ may be correlated with possible values of the (C-H) bonds' vibration frequency ($\nu_{(\text{C-H})\text{C}^{\text{C}},\text{D}}$). Hence, by taking also into account that $\Delta H_{(\text{des.})} \approx \Delta H_{(\text{C-H})\text{C}^{\text{C}},\text{D}}$, one may suppose the case of a non-diffusion-rate-controlling process corresponding to the Polanyi-Wigner model (Nechaev, 2010).

On the other hand, by taking also into account that $\Delta H_{(\text{des.})} \approx \Delta H_{(\text{C-H})\text{C}^{\text{C}},\text{D}}$, one may suppose the case of a diffusion-rate-controlling process corresponding to the TDS process IV (Table 1B). Hence, by using the value

(Nechaev, 2010) of $D_{0\text{app.IV}} \approx 6 \times 10^2 \text{ cm}^2/\text{s}$, one can evaluate the quantity of $L \approx (D_{0\text{app.IV}} / K_{0(\text{des.})})^{1/2} = 17$ nm (Table 3). The obtained value of L (also, as and in the case of (SiC-D/QFMLG) (Bocquet et al., 2012), Table 2) coincides (within the errors) with values of the quantities of $L_{\text{def.}} \approx 11 - 17$ nm [Equation (10)] and $L_{\text{def.}} \approx 20$ nm (Figure 8b). The obtained value of L is also correlated with the STM data (Figures 15 and 16). It shows that the desorption process of the intercalated hydrogen may be rate-limited by diffusion of hydrogen atoms to a nearest one of the permeable defects of the anchored graphene layer.

When interpretation of these results, one can also take into account the model (proposed in (Watcharinyanon et al., 2011) of the interaction of hydrogen and silicon atoms at the graphene-SiC interface resulted in Si-C bonds at the intercalated islands.

CONSIDERATION AND INTERPRETATION OF THE TDS/STM DATA FOR HOPG TREATED BY ATOMIC HYDROGEN

In Waqar (2007), atomic hydrogen accumulation in HOPG samples and etching their surface under hydrogen TDS have been studied by using a STM and atomic force microscope (AFM). STM investigations revealed that the

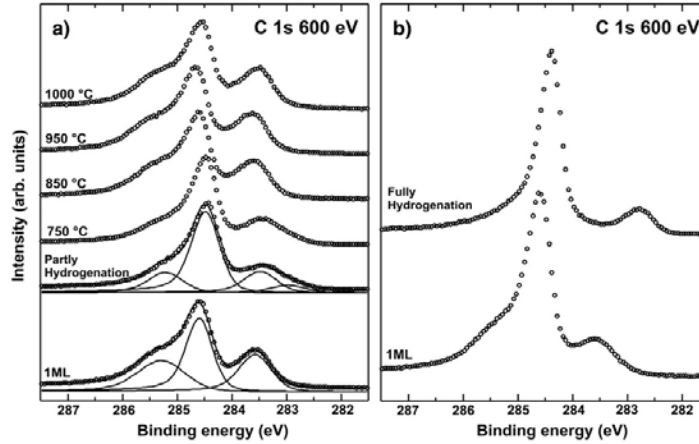


Figure 17. Normalized C 1s core level spectra of monolayer graphene (Watcharinyanon et al., 2011) before and after hydrogenation and subsequent annealing at 1023, 1123, 1223, and 1273 K. b) Fully hydrogenated graphene along with monolayer graphene before hydrogenation. The spectra were acquired at a photon energy of 600 eV.

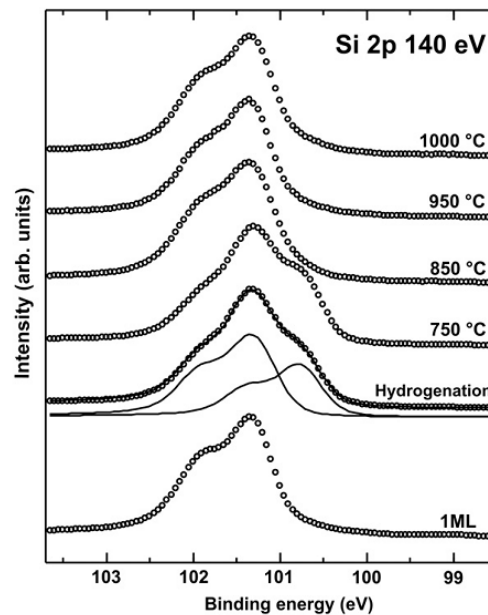


Figure 18. Normalized Si 2p core level spectra of monolayer graphene (Watcharinyanon et al., 2011) before and after hydrogenation and subsequent annealing at 1023, 1123, 1223, and 1273 K. The spectra were acquired at a photon energy of 140 eV.

surface morphology of untreated reference HOPG samples was found to be atomically flat (Figure 19a), with a typical periodic structure of graphite (Figure 19b). Atomic hydrogen exposure (treatment) of the reference HOPG samples (30 - 125 min at atomic hydrogen

pressure $P_H \approx 10^{-4}$ Pa and a near-room temperature (~ 300 K)) with different atomic hydrogen doses (D), has drastically changed the initially flat HOPG surface into a rough surface, covered with nanoblister with an average radius of ~ 25 nm and an average height of ~ 4 nm

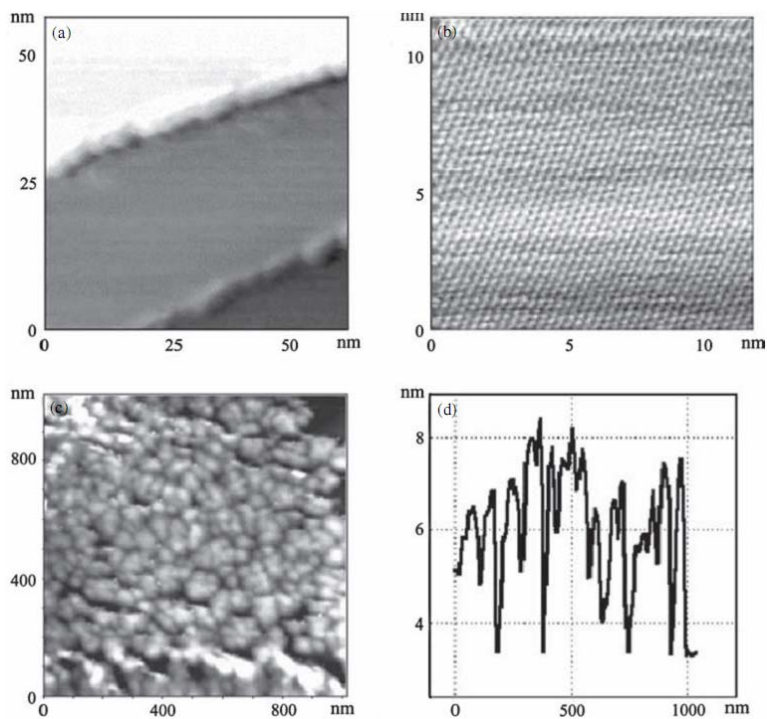


Figure 19. STM images of the untreated HOPG sample (Waqar, 2007) (under ambient conditions) taken from areas of (a) 60.8 x60.8 nm and (b) 10.9x10.9 nm (high resolution image of the square in image (a)). (c). AFM image (area of 1x1 nm) of the HOPG sample subjected to atomic hydrogen dose (D) of $1.8 \cdot 10^{16}$ H^0/cm^2 . (d) Surface height profile obtained from the AFM image reported in (c). The STM tunnel V_{bias} and current are 50-100 mV and 1-1.5 mA, respectively.

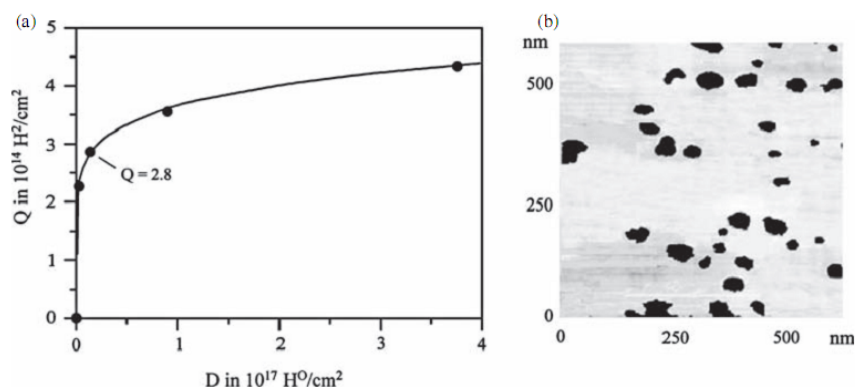


Figure 20. (a) Hydrogen storage efficiency of HOPG samples (Waqar, 2007), desorbed molecular hydrogen (Q) versus dose (D) of atomic hydrogen exposure. (b) STM image for 600x600 nm area of the HOPG sample subjected to atomic hydrogen dose of $1.8 \cdot 10^{16}$ H^0/cm^2 , followed by hydrogen thermal desorption.

(Figures 19c and d).

TDS of hydrogen has been found in heating of the HOPG samples under mass spectrometer control. As shown in Figure 20a, with the increase of the total hydrogen doses (D) to which HOPG samples have been

exposed, the desorbed hydrogen amounts (Q) increase and the percentage of D retained in samples approaches towards a saturation stage.

After TD, no nanoblister were visible on the HOPG surface, the graphite surface was atomically flat, and

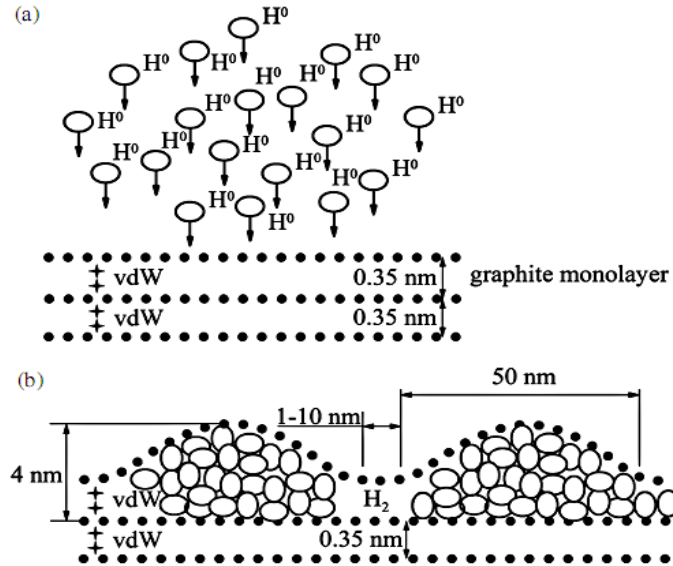


Figure 21. Model showing the hydrogen accumulation (intercalation) in HOPG, with forming blister-like nanostructures. (a) Pre-atomic hydrogen interaction step. (b) H_2 , captured inside graphene blisters, after the interaction step. Sizes are not drawn exactly in scale (Waqar, 2007).

covered with some etch-pits of nearly circular shapes, one or two layers thick (Figure 20b). This implies that after release of the captured hydrogen gas, the blisters become empty of hydrogen, and the HOPG surface restores to a flat surface morphology under the action of corresponding forces.

According to the concept by Waqar (2007), nanoblister found on the HOPG surface after atomic hydrogen exposure are simply monolayer graphite (graphene) blisters, containing hydrogen gas in molecular form (Figure 21). As suggested in Waqar (2007), atomic hydrogen intercalates between layers in the graphite net through holes in graphene hexagons, because of the small diameter of atomic hydrogen, compared to the hole's size, and is then converted to a H_2 gas form which is captured inside the graphene blisters, due to the relatively large kinetic diameter of hydrogen molecules.

However, such interpretation is in contradiction with that noted in Introduction results (Xiang et al., 2010; Jiang et al., 2009), that it is almost impossible for a hydrogen atom to pass through the six-member ring of graphene at room temperature.

It is reasonable to assume (as it has been done in some previous parts of this paper) that in HOPG (Waqar, 2007) samples atomic hydrogen passes into the graphite near-surface closed nano-regions (the graphene nanoblister) through defects (perhaps, mainly through triple junctions of the grain and/or subgrain boundary network (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011;

Koepke et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012), in the surface graphene layer. It is also expedient to note that in Figure 20b, one can imagine some grain boundary network decorated by the etch-pits.

The average blister has a radius of ~ 25 nm and a height ~ 4 nm (Figure 19). Approximating the nanoblister to be a semi-ellipse form, results in the blister area of $S_b \approx 2.0 \times 10^{-11}$ cm² and its volume $V_b \approx 8.4 \times 10^{-19}$ cm³. The amount of retained hydrogen in this sample becomes $Q \approx 2.8 \times 10^{14}$ H_2 /cm² and the number of hydrogen molecules captured inside the blister becomes $n \approx (Q S_b) \approx 5.5 \times 10^3$. Thus, within the ideal gas approximation, and accuracy of one order of the magnitude, the internal pressure of molecular hydrogen in a single nanoblister at near-room temperature ($T \approx 300$ K) becomes $P_{H_2} \approx \{k_B (Q S_b) T / V_b\} \approx 10^8$ Pa. The hydrogen molecular gas density in the blisters (at $T \approx 300$ K and $P_{H_2} \approx 1 \times 10^8$ Pa) can be estimated as $\rho \approx \{(QM_{H_2} S_b) / V_b\} \approx 0.045$ g/cm³, where M_{H_2} is the hydrogen molecule mass. It agrees with data (Trunin et al., 2010) considered in Nechaev and Veziroglu (2013), on the hydrogen (protium) isotherm of 300K.

These results can be quantitatively described, with an accuracy of one order of magnitude, with the thermodynamic approach (Bazarov, 1976), and by using the condition of the thermo-elastic equilibrium for the reaction of ($2H_{(gas)} \rightarrow H_{2(gas_in_blisters)}$), as follows (Nechaev and Veziroglu, 2013):

$$(P_{H_2}/P_{H_2}^0) \approx (P_H/P_H^0)^2 \exp\{[\Delta H_{dis} - T\Delta S_{dis} - P_{H_2}^* \Delta V] / k_B T\} \quad (11)$$

Where $P_{H_2}^*$ is related to the blister "wall" back pressure (caused by P_{H_2}) - the so called (Bazarov, 1976) surface pressure ($P_{H_2}^* \approx P_{H_2} \approx 1 \times 10^8$ Pa), P_H is the atomic hydrogen pressure corresponding to the atomic flux (Waqar, 2007) ($P_H \approx 1 \cdot 10^{-4}$ Pa), $P_{H_2}^0 = P_H^0 = 1$ Pa is the standard pressure, $\Delta H_{dis} = 4.6$ eV is the experimental value (Karapet'yants and Karapet'yants, 1968) of the dissociation energy (enthalpy) of one molecule of gaseous hydrogen (at room temperatures), $\Delta S_{dis} = 11.8$ k_B is the dissociation entropy (Karapet'yants and Karapet'yants, 1968), $\Delta V \approx (S_b r_b / n)$ is the apparent volume change, r_b is the radius of curvature of nanoblister at the nanoblister edge ($r_b \approx 30$ nm, Figures 19 and 21b), N_A is the Avogadro number, and T is the temperature ($T \approx 300$ K). The quantity of ($P_{H_2}^* \Delta V$) is related to the work of the nanoblister surface increasing with an intercalation of 1 molecule of H_2 .

The value of the tensile stresses σ_b (caused by $P_{H_2}^*$) in the graphene nanoblister "walls" with a thickness of d_b and a radius of curvature r_b can be evaluated from another condition (equation) of the thermo-elastic equilibrium of the system in question, which is related to Equation 11 as follows (Nechaev and Veziroglu, 2013):

$$\sigma_b \approx (P_{H_2}^* r_b / 2 d_b) \approx (\varepsilon_b E_b) \quad (12)$$

Where ε_b is a degree of elastic deformation of the graphene nanoblister walls, and E_b is the Young's modulus of the graphene nanoblister walls. Substituting in the first part of Equation (12), the quantities of $P_{H_2}^* \approx 1 \times 10^8$ Pa, $r_b \approx 30$ nm and $d_b \approx 0.15$ nm results in the value of $\sigma_{b[15]} \approx 1 \times 10^{10}$ Pa.

The degree of elastic deformation of the graphene nanoblister walls, apparently reaches $\varepsilon_{b[15]} \approx 0.1$ (Figure 21b). Hence, with Hooke's law of approximation, using the second part of Equation (12), one can estimate, with the accuracy of one-two orders of the magnitude, the value of the Young's modulus of the graphene nanoblister walls: $E_b \approx (\sigma_b / \varepsilon_b) \approx 0.1$ TPa. It is close (within the errors) to the experimental value (Lee et al., 2008; Pinto and Leszczynski, 2014) of the Young's modulus of a perfect (that is, without defects) graphene ($E_{graphene} \approx 1.0$ TPa).

The experimental data (Waqar, 2007; Waqar et al., 2010) on the TDS (the flux J_{des}) of hydrogen from graphene nanoblister in pyrolytic graphite can be approximated by three thermodesorption (TDS) peaks, that is, #1 with $T_{max\#1} \approx 1123$ K, #2 with $T_{max\#2} \approx 1523$ K, and #3 with $T_{max\#3} \approx 1273$ K. But their treatment, with using the above mentioned methods (Nechaev, 2010), is difficult due to some uncertainty relating to the zero level of the J_{des} quantity.

Nevertheless, TDS peak #1 (Waqar et al., 2010) can be characterized by the activation desorption energy

$\Delta H_{(des.)1[59]} = 2.4 \pm 0.5$ eV, and by the per-exponential factor of the reaction rate constant of $K_{0(des.)1[59]} \approx 2 \times 10^{10}$ s^{-1} (Table 3). It points that TDS peak 1 (Waqar et al., 2010) may be related to TDS peak (process) III, for which the apparent diffusion activation energy is $Q_{app.III} = (2.6 \pm 0.3)$ eV and $D_{0app.III} \approx 3 \times 10^{-3}$ cm^2/s (Table 1B). Hence, one can obtain (with accuracy of one-two orders of the magnitude) a reasonable value of the diffusion characteristic size of $L_{TDS-peak1[59]} \approx (D_{0app.III}/K_{0(des.)1[59]})^{1/2} \approx 4$ nm, which is obviously related to the separating distance between the graphene nanoblister (Figure 21b) or (within the errors) to the separation distance between etch-pits (Figure 20b) in the HOPG specimens (Waqar, 2007; Waqar et al., 2010).

As noted in the previous parts of this paper, process III is related to model "F*" (Yang and Yang, 2002) (with $\Delta H_{(C-H)F^*} = (2.5 \pm 0.3)$ eV (Nechaev, 2010), and it is a rate-limiting by diffusion of atomic hydrogen between graphene-like layers (in graphite materials and nanomaterials), where molecular hydrogen cannot penetrate (according to analysis (Nechaev, 2010) of a number of the related experimental data).

Thus, TDS peak (process) 1 (Waqar, 2007; Waqar et al., 2010) may be related to a rate-limiting diffusion of atomic hydrogen, between the surface graphene-like layer and neighboring (near-surface) one, from the graphene nanoblister to the nearest penetrable defects of the separation distance $L_{TDS-peak1[59]} \sim 4$ nm.

As considered below, a similar (relevance to results (Waqar, 2007; Waqar et al., 2010) situation, with respect to intercalation of a high density molecular hydrogen into closed (in the definite sense) nanoblister and/or nanoregions in graphene-layer-structures, may occur in hydrogenated GNFs.

A POSSIBILITY OF INTERCALATION OF SOLID H_2 INTO CLOSED NANOREGIONS IN HYDROGENATED GRAPHITE NANOFIBERS (GNFS) RELEVANT TO THE HYDROGEN ON-BOARD STORAGE PROBLEM

The possibility of intercalation of a high density molecular hydrogen (up to solid H_2) into closed (in the definite sense) nanoregions in hydrogenated GNFs is based both on the analytical results presented in the previous parts of this study (Tables 1 to 3), and on the following facts (Nechaev and Veziroglu, 2013):

(1) According to the experimental and theoretical data (Trunin et al., 2010) (Figures 22 and 23), a solid molecular hydrogen (or deuterium) of density of $\rho_{H_2} = 0.3 - 0.5$ g/cm^3 (H_2) can exist at 300K and an external pressure of $P = 30 - 50$ GPa.

(2) As seen from data in Figures 19 to 21 and Equations 11 and 12, the external (surface) pressure of $P = P_{H_2}^* = 30$ to 50 GPa at $T \approx 300$ K may be provided at the expense of the association energy of atomic hydrogen ($T\Delta S_{dis} - \Delta H_{dis}$), into some closed (in the definite sense) nano-

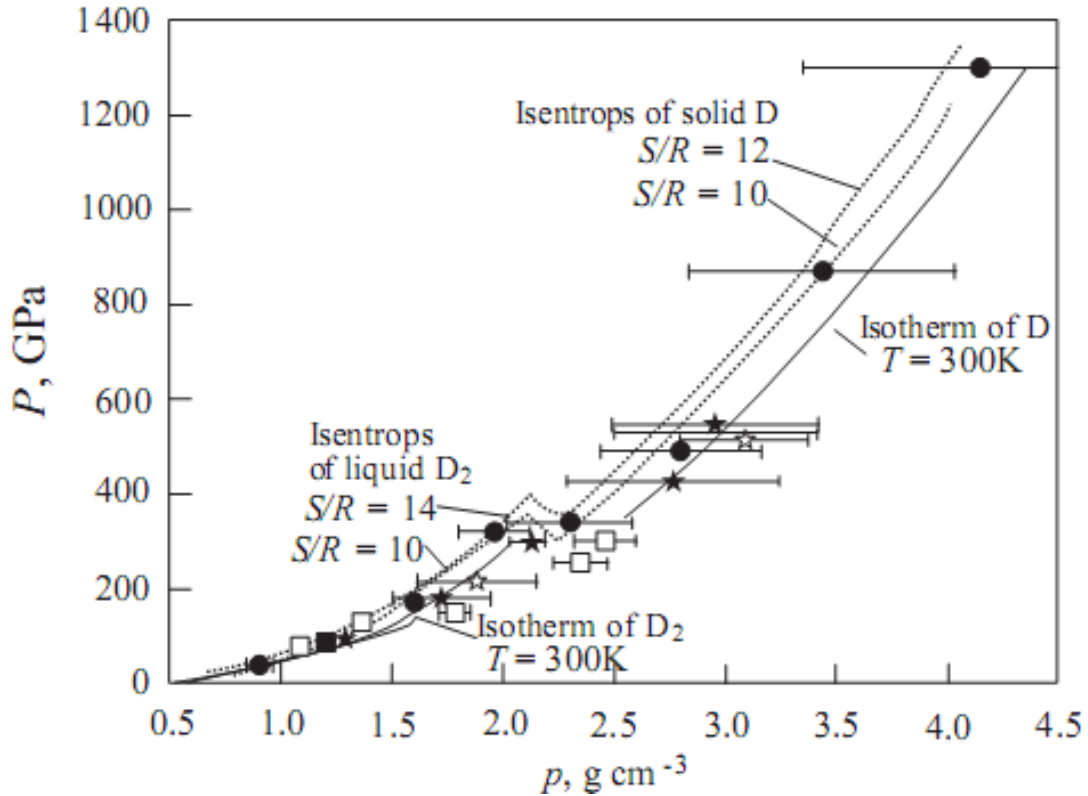


Figure 22. Isentropes (at entropies $S/R = 10, 12$ and 14 , in units of the gas constant R) and isotherms (at $T = 300$ K) of molecular and atomic deuterium (Trunin et al., 2010). The symbols show the experimental data, and curves fit calculated dependences. The density (ρ) of protium was increased by a factor of two (for the scale reasons). Thickened portion of the curve is an experimental isotherm of solid form of molecular hydrogen (H_2). The additional red circle corresponds to a value of the twinned density $\rho \approx 1$ g/cm³ of solid H_2 (at $T \approx 300$ K) and a near-megabar value of the external compression pressure $P \approx 50$ GPa (Nechaev and Veziroglu, 2013).

regions in hydrogenated (in gaseous atomic hydrogen with the corresponding pressure P_H) graphene-layer-nanostructures possessing of a high Young's modulus ($E_{\text{graphene}} \approx 1$ TPa).

(3) As shown in Nechaev and Veziroglu (2013), the treatment of the extraordinary experimental data (Gupta et al., 2004) (Figure 24) on hydrogenation of GNFs results in the empirical value of the hydrogen density $\rho_{H_2} = (0.5 \pm 0.2)$ g(H_2)/cm³(H_2) (or $\rho_{(H_2-C\text{-system})} \approx 0.2$ g(H_2)/cm³(H_2 -C-system)) of the intercalated (at $T \approx 300$ K) high-purity reversible hydrogen (about 17 mass% H_2); it corresponds to the state of solid molecular hydrogen at the pressure of $P = P^*_{H_2} \approx 50$ GPa, according to data from Figures 22 and 23.

(4) Substituting in Equation (12) the quantities of $P^*_{H_2} \approx 5 \times 10^{10}$ Pa, $\varepsilon_b \approx 0.1$ (Figure 24), the largest possible value of $E_b \approx 10^{12}$ Pa (Lee et al., 2008; Pinto and Leszczynski (2014)), the largest possible value of the tensile stresses ($\sigma_b \approx 10^{11}$ Pa (Lee et al., 2008; Pinto and Leszczynski, 2014) in the edge graphene "walls" (of a thickness of d_b and a radius of curvature of r_b) of the slit-like closed nanopores of the lens shape (Figure 24), one can obtain

the quantity of $(r_b / d_b) \approx 4$. It is reasonable to assume $r_b \approx 20$ nm; hence, a reasonable value follows of $d_b \approx 5$ nm.

(5) As noted in (Nechaev and Veziroglu, 2013), a definite residual plastic deformation of the hydrogenated graphite (graphene) nano-regions is observed in Figure 24. Such plastic deformation of the nanoregins during hydrogenation of GNFs may be accompanied with some mass transfer resulting in such thickness (d_b) of the walls.

(6) The related data (Figure 25) allows us to reasonably assume a break-through in results (Nechaev and Veziroglu, 2013) on the possibility (and particularly, physics) of intercalation of a high density molecular hydrogen (up to solid H_2) into closed (in the definite sense) nanoregions in hydrogenated GNFs (Gupta et al., 2004; Park et al., 1999), relevant for solving of the current problem (Akiba, 2011; Zuetzel, 2011; DOE targets, 2012) of the hydrogen on-board effective storage.

(7) Some fundamental aspects - open questions on engineering of "super" hydrogen storage carbonaceous nanomaterials, relevance for clean energy applications, are also considered in (Nechaev and Veziroglu, 2013) and in this study, as well.

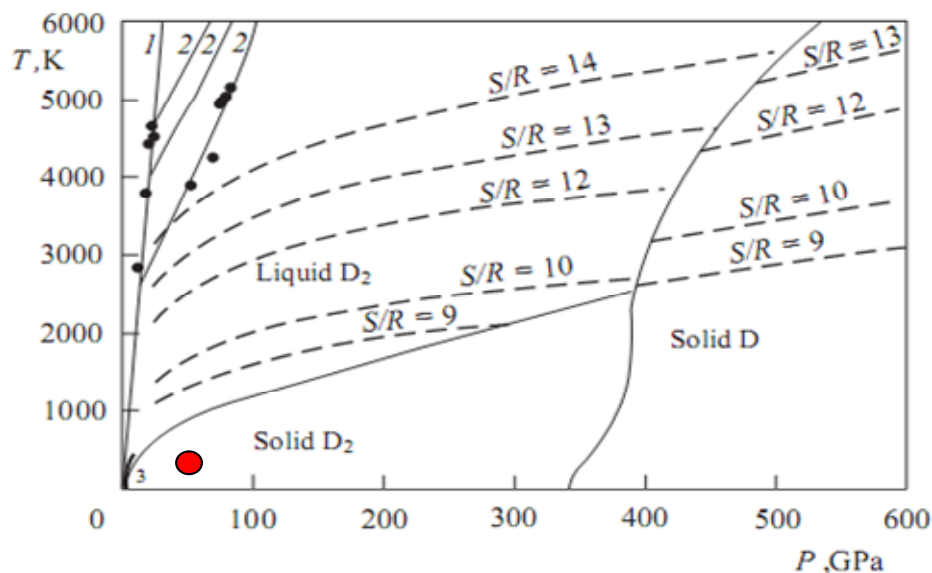


Figure 23. Phase diagram (Trunin et al., 2010), adiabats, and isentropes of deuterium calculated with the equation of state: 1 and 2 are a single and a doubled adiabat, ● – the experimental data, 3 – melting curve, thickened portion of the curve – the experimental data. The additional red circle corresponds to a value of temperature $T \approx 300$ K and a near-megabar value of the external compression pressure $P \approx 50$ GPa (Nechaev and Veziroglu, 2013).

DISCUSSION

On the “thermodynamic forces” and/or energetics of forming (under atomic hydrogen treatment) of graphene nanoblusters in the surface HOPG layers and epitaxial graphenes

A number of researchers (Waqar, 2007; Watcharinyanon et al., 2011; Wojtaszek et al., 2011; Castellanos-Gomez et al., 2012; Bocquet et al., 2012; Hornekaer et al., 2006; Luo et al., 2009; Balog et al., 2009; Waqar et al., 2010) have not sufficiently considered the “thermodynamic forces” and/or energetics of forming (under atomic hydrogen treatment) graphene nanoblusters in the surface HOPG layers and epitaxial graphenes.

Therefore, in this study, the results of the thermodynamic analysis (Equations 11 and 12) are presented, which may be used for interpretation of related data (Figures 6 to 8, 11 to 16, 19 to 21).

On some nanodefects (grain boundaries, their triple junctions and others), penetrable for atomic hydrogen, in the surface HOPG graphene-layers and epitaxial graphenes

A number of researchers noted above have not taken into account (in a sufficient extent) the calculation results (Xiang et al., 2010) showing that the barrier for the penetration of a hydrogen atom through the six-member

ring of a perfect graphene is larger than 2.0 eV. Thus, it is almost impossible for a hydrogen atom to pass through the six-member ring of a perfect (that is, without defects) graphene layer at room temperature.

Therefore, in this study, a real possibility of the atomic hydrogen penetration through some nanodefects in the graphene-layer-structures, that is, grain boundaries, their triple junctions (nodes) and/or vacancies (Brito et al., 2011; Zhang et al., 2014; Banhart et al., 2011; Yazyev and Louie, 2010; Kim et al., 2011; Koepke et al., 2013; Zhang and Zhao, 2013; Yakobson and Ding, 2011; Cockayne et al., 2011; Zhang et al., 2012; Eckmann et al., 2012), are considered. These analytical results may be used for interpretation of the related data (for instance, Figures 6 to 8, 11 to 16, 19 to 21).

On finding and interpretation of the thermodynamic characteristics of “reversible” hydrogenation-dehydrogenation of epitaxial graphenes and membrane ones

A number of researchers, for instance ones noted above have not treated and compared their data on “reversible” hydrogenation-dehydrogenation of membrane graphenes and epitaxial ones, with the aim of finding and interpretation of the thermodynamic characteristics. Therefore, in this analytical study, the thermodynamic approaches (particularly, Equations 1 to 12), such

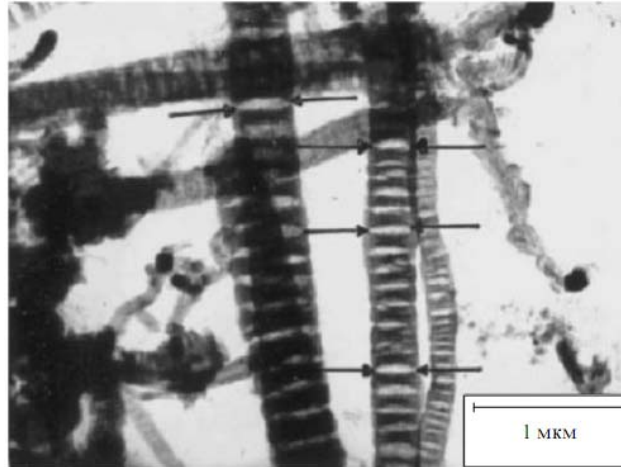


Figure 24. Micrographs (Gupta et al., 2004) of hydrogenated graphite nanofibers (GNFs) after release from them (at ~300 K for ~10 min (Park et al., 1999) of intercalated high-density hydrogen (~17 mass.% - the gravimetric reversible hydrogen capacity). The arrows in the picture indicate some of the slit-like closed nanopores of the lens shape, where the intercalated high-density solid hydrogen nanophase (Nechaev and Veziroglu, 2013) was localized.

Mass and Volume Densities

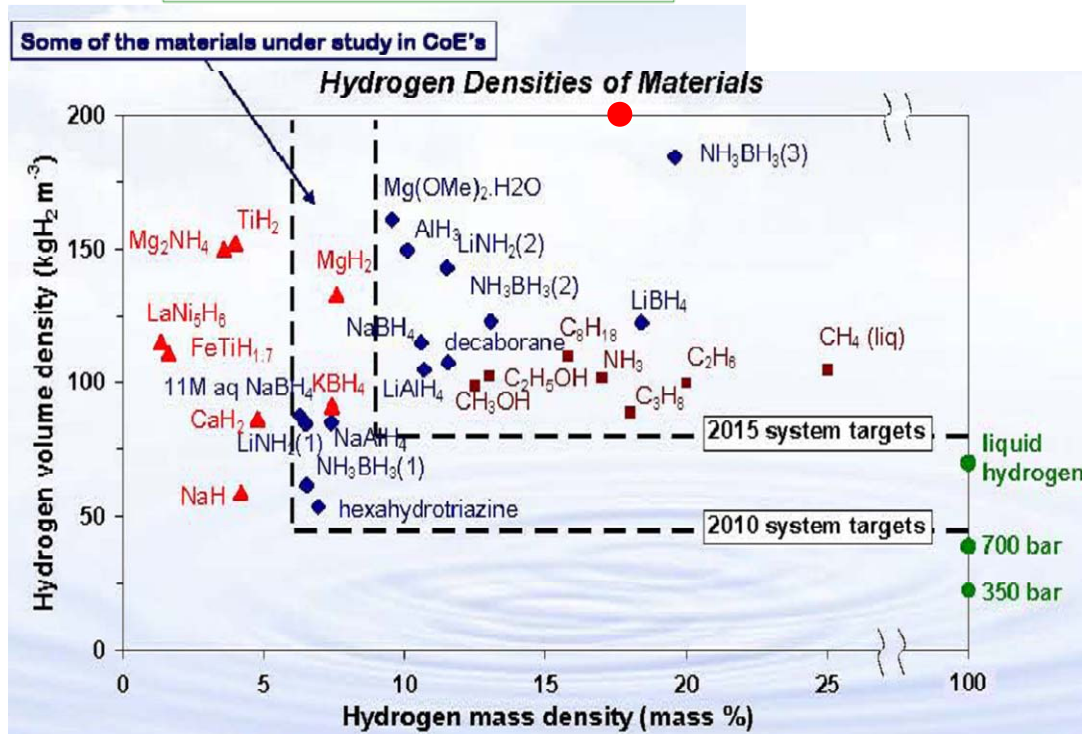


Figure 25. It is shown (in the face of known achievements) U.S. DOE system targets for 2010 and 2015, relevant to gravimetric and volumetric hydrogen on-board storage densities. The additional red circle is related to the solid hydrogen nanophase (Nechaev and Veziroglu, 2013) intercalated into the hydrogenated GNFs (Figure 24).

treatment results of related theoretical and experimental data (Tables 1 to 3) and their interpretation are presented. As shown, these analytical results may be used for a more detailed understanding and revealing of the atomic mechanisms of the processes.

There is a considerable difference (in the declared errors and without any explanation) in the theoretical values of the energetic graphene (CH) quantities ($\Delta H_{(C-H)}$, $\Delta H_{(bind.)}$, $\Delta H_{(C-C)}$) obtained in different theoretical studies, for instance, in (Sofa et al., 2007; Dzhurakhalov and Peeters, 2011) (Table 1A).

Unfortunately, the theoretical values of the graphene quantity of $\Delta H_{(C-C)}$ is usually not evaluated by the researchers, and not compared by them with the much higher values of the graphene (both theoretical, and experimental) quantity of $\Delta H_{(C-C)}$ (Table 1A). It could be useful, for instance, when considering the fundamental strength properties of graphene and graphene structures. As far as we know, most researchers have not taken into account the alternative possibility supposed in (Elias et al., 2009) that (i) the experimental graphene membrane (a free-standing one) may have “a more complex hydrogen bonding, than the suggested by the theory”, and that (ii) graphane (CH) (Sofa et al., 2007) may be the until now theoretical material.

In this connection, it seems expedient to take into account also some other approaches and results (Sorokin and Chernozatonskii, 2013; Davydov and Lebedev, 2012; Khusnutdinov, 2012; Chernozatonskii et al., 2012; Data et al., 2012).

On the thermodynamic characteristics and atomic mechanisms of “reversible” hydrogenation-dehydrogenation of free-standing graphene membranes

The thermodynamic analysis of experimental data (Elias et al., 2009) on “reversible” hydrogenation-dehydrogenation of free-standing graphene membranes have resulted in the following conclusive suppositions and/or statements:

(1) These chemisorption processes are related to a non-diffusion-rate-limiting case. They can be described and interpreted within the physical model of the Polanyi-Wigner equation for the first order rate reactions (Nechaev, 2010; Nechaev and Veziroglu, 2013), but not for the second order rate ones (Zhao et al., 2006).

(2) The desorption activation energy is of $\Delta H_{des.(membr.[5])} = \Delta H_{C-H(membr.[5])} = 2.6 \pm 0.1$ eV (Table 1A). The value of the quantity of $\Delta H_{C-H(membr.[5])}$ coincides (within the errors), in accordance with the Polanyi-Wigner model, with the values of the similar quantities for theoretical graphenes (Sofa et al., 2007; Openov and Podlivaev, 2010) (Table 1A) possessing of a diamond-like distortion of the graphene network. The value of the quantity of ΔH_C

$H_{(membr.[5])}$ coincides (within the errors) with the value of the similar quantity for model “F*” (Table 1B) manifested in graphitic structures and nanostructures not possessing of a diamond-like distortion of the graphene network (an open theoretical question).

(3) The desorption frequency factor is of $K_{0des.(membr.[5])} = \nu_{C-H(membr.[5])} \approx 5 \times 10^{13}$ s⁻¹ (Table 1A); it is related to the corresponding vibration frequency for the C-H bonds (in accordance with the Polanyi-Wigner model for the first order rate reactions).

(4) The adsorption activation energy (in the approximation of $K_{0ads.} \approx K_{0des.}$) is of $\Delta H_{ads.(membr.[5])} = 1.0 \pm 0.2$ eV (Table 1A). The heat of adsorption of atomic hydrogen by the free standing graphene membranes (Elias et al., 2009) can be evaluated as: $(\Delta H_{ads.(membr.[5])} - \Delta H_{des.(membr.[5])}) = -1.5 \pm 0.2$ eV (an exothermic reaction).

(5) Certainly, these tentative analytical results could be directly confirmed and/or modified by receiving and treating (within Equations (8) and (9) approach) of the experimental data on $\tau_{0.63}$ at several annealing temperatures.

On the thermodynamic characteristics and atomic mechanisms of “reversible” hydrogenation-dehydrogenation of epitaxial graphenes

The thermodynamic analyses of experimental data (Waqar, 2007; Watcharinyanon et al., 2011; Wojtaszek et al., 2011; Castellanos-Gomez et al., 2012; Bocquet et al., 2012; Luo et al., 2009) on “reversible” hydrogenation-dehydrogenation of epitaxial graphenes have resulted in the following conclusive suppositions and/or statements:

(1) These chemisorption processes for all 16 considered epitaxial graphenes (Tables 1A, 2 and 3), unlike ones for the free-standing graphene membranes (Table 1A), are related to a diffusion-rate-limiting case. They can be described and interpreted within the known diffusion approximation of the first order rate reactions (Nechaev, 2010; Nechaev and Veziroglu, 2013), but not within the physical models of the Polanyi-Wigner equations for the first (Hornekaer et al., 2006) or for the second (Zhao et al., 2006) order rate reactions.

(2) The averaged desorption activation energy for 14 of 16 considered epitaxial graphenes (Tables 1A, 2 and 3) is of $\Delta H_{des.(epitax.)} = 0.5 \pm 0.4$ eV, and the averaged quantity of $\ln K_{0des.(epitax.)} = 5 \pm 8$, that is, $K_{0des.(epitax.)} \approx 1.5 \times 10^2$ s⁻¹ (or $5 \times 10^{-2} - 5 \times 10^5$ s⁻¹); the adsorption activation energy (in a rough approximation of $K_{0ads.} \approx K_{0des.}$) is of $\Delta H_{ads.(epitax.)} = 0.3 \pm 0.2$ eV.

(3) The above obtained values of characteristics of dehydrogenation of the epitaxial graphenes can be presented, as follows: $\Delta H_{des.} \sim Q_{app.I}$, $K_{0des.} \sim (D_{0app.I} / L^2)$, where $Q_{app.I}$ and $D_{0app.I}$ are the characteristics of process I (Table 1B), $L \sim d_{sample}$, that is, being of the order of diameter (d_{sample}) of the epitaxial graphene samples. The

diffusion-rate-limiting process I is related to the chemisorption models “F” and “G” (Figure 4). These results unambiguously point that in the epitaxial graphenes the dehydrogenation processes are rate-limiting by diffusion of hydrogen, mainly, from chemisorption “centers” (of “F” and/or “G” types (Figure 4) localized on the internal graphene surfaces to the frontier edges of the samples. These results also point that the solution and the diffusion of molecular hydrogen may occur between the graphene layer and the substrate, unlike for a case of the graphene neighbor layers in graphitic structures and nanostructures, where the solution and the diffusion of only atomic hydrogen (but not molecular one) can occur (process III (Nechaev, 2010), Table 1B).

(4) The above formulated interpretation (model) is direct opposite to the supposition (model) of a number of researchers, those believe in occurrence of hydrogen desorption (dehydrogenation) processes, mainly, from the external epitaxial graphene surfaces. And it is direct opposite to the supposition - model of many scientists that the diffusion of hydrogen along the graphene-substrate interface is negligible.

(5) In this connection, it is expedient to take into account also some other related experimental results, for instance (Stolyarova et al., 2009; Riedel et al., 2009; Riedel et al., 2010; Goleret et al., 2013; Jones et al., 2012; Lee et al., 2012), on the peculiarities of the hydrogenation-dehydrogenation processes in epitaxial graphenes, particularly, in the graphene-substrate interfaces.

Conclusion

(1) The chemisorption processes in the free-standing graphene membranes are related to a non-diffusion-rate-limiting case. They can be described and interpreted within the physical model of the Polanyi-Wigner equation for the first order rate reactions, but not for the second order rate reactions.

The desorption activation energy is of $\Delta H_{\text{des. (membr.)}} = \Delta H_{\text{C-H (membr.)}} = 2.6 \pm 0.1$ eV. It coincides (within the errors), in accordance with the Polanyi-Wigner model, with the values of the similar quantities for theoretical graphanes (Table 1A) possessing of a diamond-like distortion of the graphene network. It also coincides (within the errors) with the value of the similar quantity [process III, model “F*” (Table 1B)] manifested in graphitic structures and nanostructures, not possessing of a diamond-like distortion of the graphene network (an open theoretical question).

The desorption frequency factor is of $K_{0\text{des. (membr.)}} = \nu_{\text{C-H (membr.)}} \approx 5 \times 10^{13} \text{ s}^{-1}$ (Table 1A). It is related to the corresponding vibration frequency for the C-H bonds (in accordance with the Polanyi-Wigner model).

The adsorption activation energy (in the approximation of $K_{0\text{ads.}} \approx K_{0\text{des.}}$) is of $\Delta H_{\text{ads. (membr.)}} = 1.0 \pm 0.2$ eV (Table

1A). The heat of adsorption of atomic hydrogen by the free standing graphene membranes (Elias et al., 2009) may be as $(\Delta H_{\text{ads. (membr.)}} - \Delta H_{\text{des. (membr.)}}) = -1.5 \pm 0.2$ eV (an exothermic reaction).

(2) The hydrogen chemisorption processes in epitaxial graphenes (Tables 1A, 2 and 3), unlike ones for the free-standing graphene membranes (Table 1A), are related to a diffusion-rate-limiting case. They can be described and interpreted within the known diffusion approximation of the first order rate reactions, but not within the physical models of the Polanyi-Wigner equations for the first or for the second order rate reactions.

The desorption activation energy is of $\Delta H_{\text{des. (epitax.)}} = 0.5 \pm 0.4$ eV. The quantity of $\ln K_{0\text{des. (epitax.)}}$ is of 5 ± 8 , and the per-exponential factor of the desorption rate constant is of $K_{0\text{des. (epitax.)}} \approx 1.5 \times 10^2 \text{ s}^{-1}$ (or $5 \times 10^2 - 5 \times 10^5 \text{ s}^{-1}$). The adsorption activation energy (in a rough approximation of $K_{0\text{ads.}} \approx K_{0\text{des.}}$) is of $\Delta H_{\text{ads. (epitax.)}} = 0.3 \pm 0.2$ eV.

The above obtained values of characteristics of dehydrogenation of the epitaxial graphenes can be presented as $\Delta H_{\text{des.}} \sim Q_{\text{app. I}}$ and $K_{0\text{des.}} \sim (D_{0\text{app. I}} / L^2)$, where $Q_{\text{app. I}}$ and $D_{0\text{app. I}}$ are the characteristics of process I (Table 1B), $L \sim d_{\text{sample}}$, that is, being of the order of diameter (d_{sample}) of the epitaxial graphene samples. The diffusion-rate-limiting process I is related to the chemisorption models “F” and “G” (Figure 4). These results unambiguously point that in the epitaxial graphenes the dehydrogenation processes are rate-limiting by diffusion of hydrogen, mainly, from chemisorption “centers” [of “F” and/or “G” types (Figure 4)] localized on the internal graphene surfaces to the frontier edges of the samples. These results also point that the solution and the diffusion of molecular hydrogen occurs in the interfaces between the graphene layers and the substrates. It differs from the case of the graphene neighbor layers in graphitic structures and nanostructures, where only atomic hydrogen solution and diffusion can occur (process III, model “F*”, Table 1B). Such an interpretation (model) is direct opposite, relevance to the supposition (model) of a number of researchers, those believe in occurrence of hydrogen desorption processes, mainly, from the external epitaxial graphene surfaces. And it is direct opposite to the supposition-model of many scientists that the diffusion of hydrogen along the graphene-substrate interface is negligible.

(3) The possibility, and particularly, the physics of intercalation of a high density molecular hydrogen (up to solid H_2) in closed nanoregions, in hydrogenated GNFs have been discussed, in connection to the analytical results (Tables 1 to 3) and the empirical facts considered in this paper.

It is relevant for developing of a key breakthrough nanotechnology of the hydrogen on-board efficient and compact storage (Figure 25) - the very current problem.

Such a nanotechnology may be developed within a reasonable (for the current hydrogen energy demands

and predictions) time frame of several years. International cooperation is necessary.

Conflict of Interest

The author(s) have not declared any conflict of interest.

ACKNOWLEDGMENTS

The authors are grateful to A. Yürüm, A. Tekin, N. K. Yavuz and Yu. Yürüm, participants of the joint RFBR-TUBAK project, for helpful and fruitful discussions. This work has been supported by the RFBR (Project #14-08-91376 CT) and the TUBITAK (Project # 213M523).

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